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Process simulation for advanced stress and junction engineering

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Submitted on 8 Feb 2012

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ESSDERC/ESSCIRC Tutorial 2008: Characterisation for the nanoelectric era

Process simulation for advanced stress and junction engineering

Christophe Krzeminski and Evelyne Lampin

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59652 Villeneuve d'Ascq

France



Tutorial objectives

“Process simulation for advanced stress and junction engineering”

» Large topic and only 45 minutes !

» and 53 slides

» Why Simulation in a characterisation tutorial ?

» Complementary...

» Not a so good idea to go deeply in the modeling aspect

» Overview of the field: the challenge (Part I), status (Part II), progress (Part III & IV) and perspectives (Part V)

» No equation

Part I: Introduction: Challenge and solution for downscaling

Part II: Process simulation ?

Part III: Recent progress in the modeling of stress

Part IV: Recent progress in the modeling of junction engineering

Part V: Perspectives in Atomistic TCAD: towards some atomistic experiment ?

Part I Introduction: Challenge and solution for downscaling

Downscaling (→ 90 nm)

26

IEEE TRANSACTIONS ON SEMICONDUCTOR MANUFACTURING, VOL. 18, NO. 1, FEBRUARY 2005

In Search of “Forever,” Continued Transistor Scaling One New Material at a Time

Scott E. Thompson, *Senior Member, IEEE*, Robert S. Chau, *Senior Member, IEEE*, Tahir Ghani, Kaizad Mistry, Sunit Tyagi, *Member, IEEE*, and Mark T. Bohr, *Fellow, IEEE*

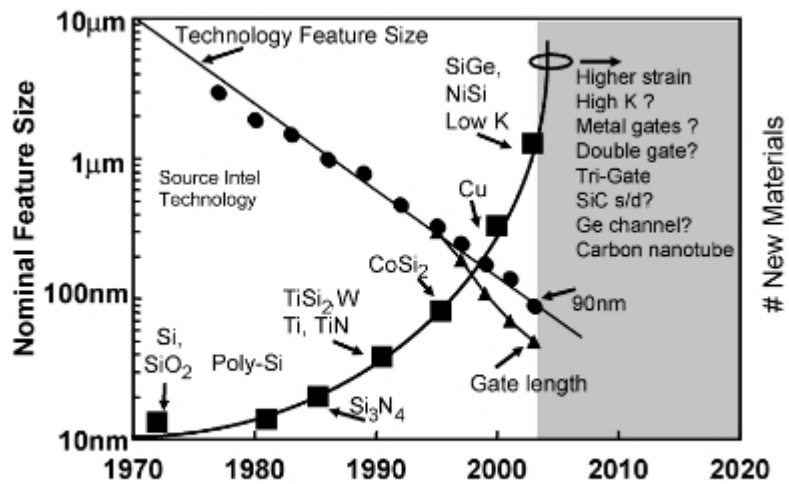
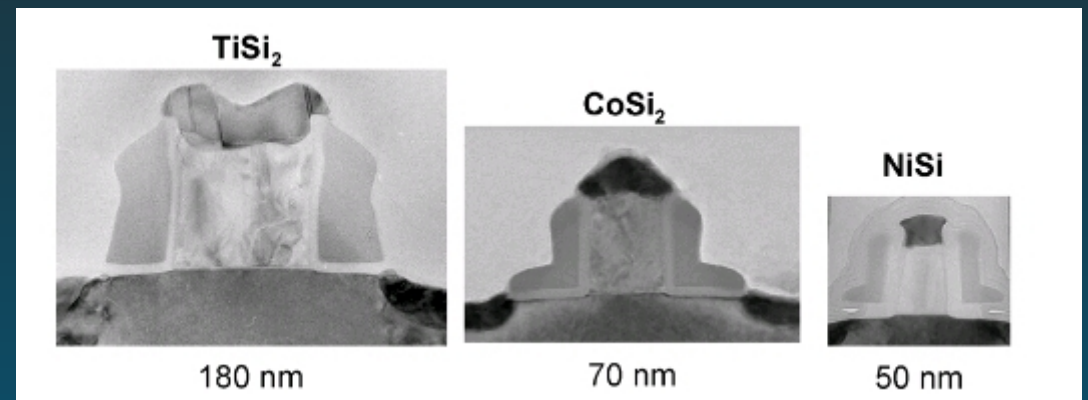


Fig. 2. Feature size and new materials versus year.



S. E. Thompson et al., IEEE Trans. On Semiconductor Manufacturing, Vol. 18, n°1, 2005

Downscaling (→ 90 nm)

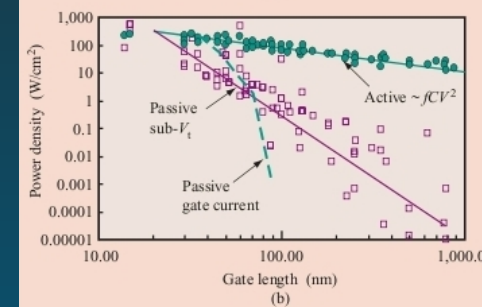
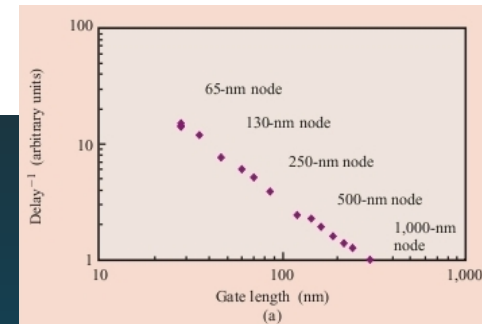
Silicon CMOS devices beyond scaling

To a large extent, scaling was not seriously challenged in the past. However, a closer look reveals that early signs of scaling limits were seen in high-performance devices in recent technology nodes. To obtain the projected performance gain of 30% per generation, device designers have been forced to relax the device subthreshold leakage continuously from one to several nA/μm for the 250-nm node to hundreds of nA/μm for the 65-nm node. Consequently, passive power density is now a significant portion of the power budget of a high-speed microprocessor.

W. Haensch
E. J. Nowak
R. H. Dennard
P. M. Solomon
A. Bryant
O. H. Dokumaci
A. Kumar
X. Wang
J. B. Johnson
M. V. Fischetti

Table 1 Relationships for constant-field scaling and for generalized field scaling. α is the scaling factor for dimensions, and $E = V/\alpha$ is the normalized electric field.

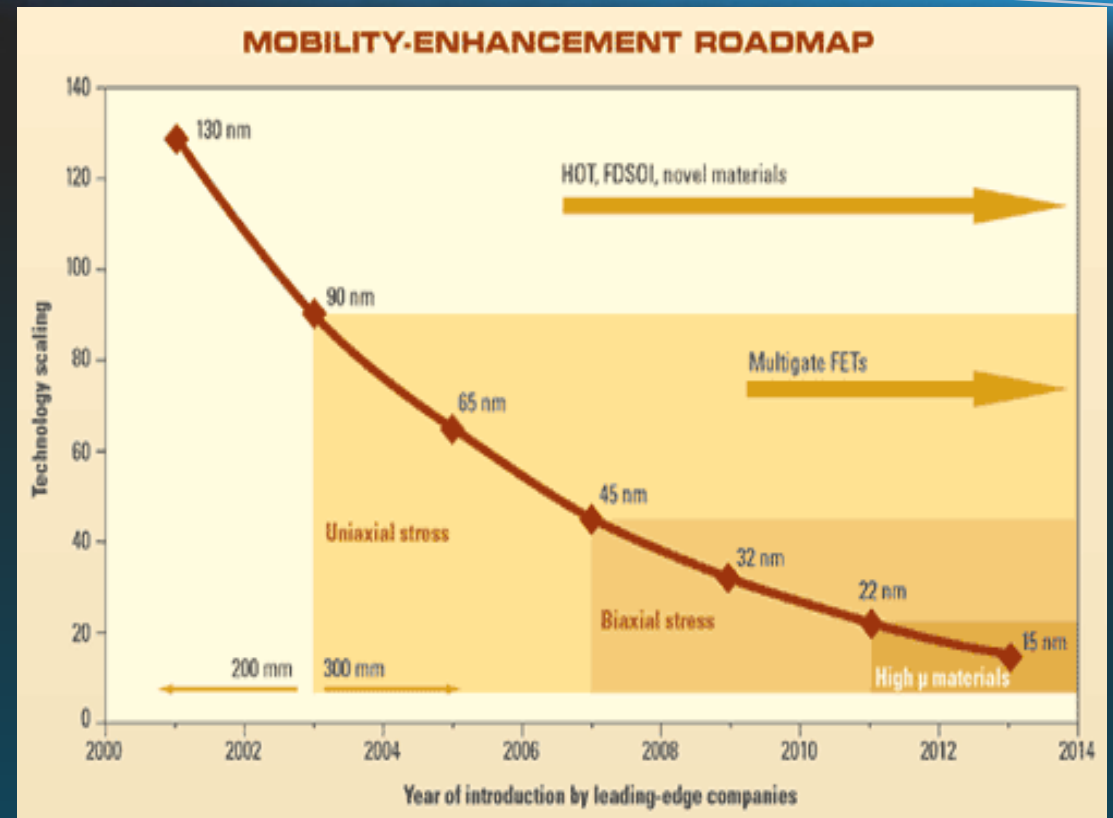
Parameter	Constant-field scaling	Generalized field scaling
Physical dimensions, L, W, T_{ox} , wire pitch	$1/\alpha$	$1/\alpha$
Body doping concentration	α	E/α
Voltage	$1/\alpha$	E/α
Circuit density	$1/\alpha^2$	$1/\alpha^2$
Capacitance per circuit	$1/\alpha$	$1/\alpha$
Circuit speed	α	α (goal)
Circuit power	$1/\alpha^2$	E^2/α^2
Power density	1	E^2
Power-delay product (energy per operation)	$1/\alpha^2$	E^2/α^3



W. Haensch et al., IBM J. Res&Dev, Vol. 50, n°45, 2006

Stress Engineering approach

- (90nm → ?)



Mohta et al., IEEE Circuits and Magazine 2005

L. Peters, "Options Narrow at 45nm", Semiconductor International, 2006

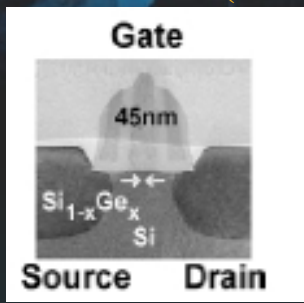
Main idea: Strain engineering for enhanced mobility and drive current

Uniaxial stress techniques

PMOS

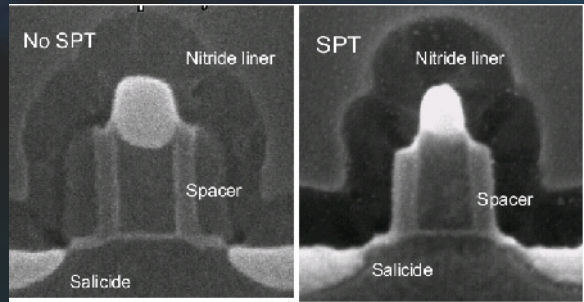
NMOS

SiGe stressor (eSiGe)



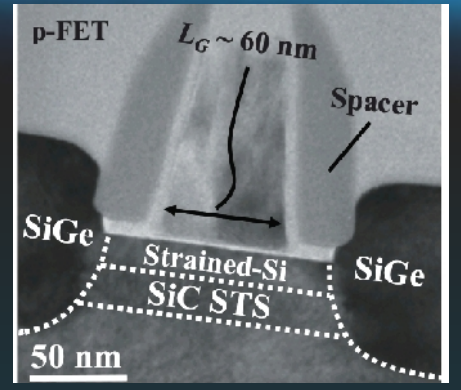
T. Ghani et al., IEDM 2003

Stress Proximity Technique (SPT)



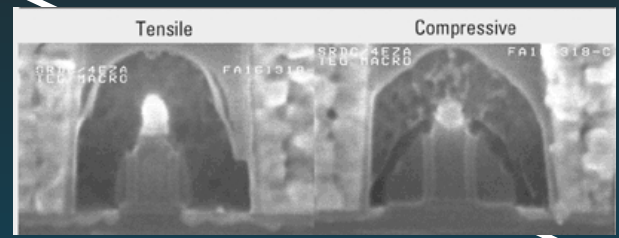
X. Chen et al., VLSI 2006

Strain Transfer Structure (STS)



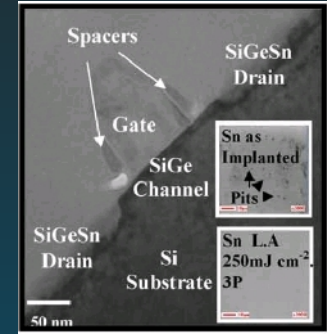
H. S. Ang et al., VLSI 2007

Dual Stress Liner (DSL)



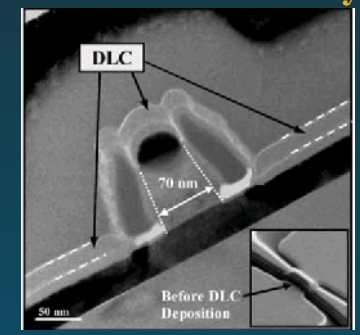
H. S. Yang et al., IEDM 2004

SiGeSn Stressor



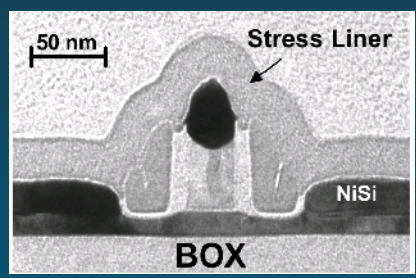
Wang, IEDM 2007

Diamond Like Carbon layer (DLC)



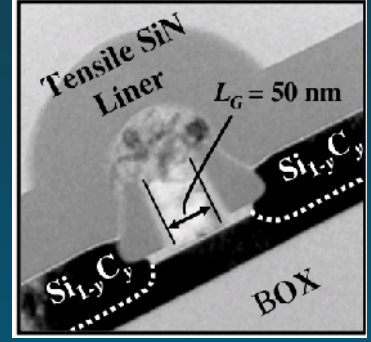
Tan, IEDM 2007

Stress Memorization (SMT)



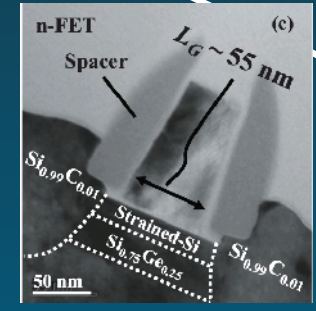
V. Singh et al., IEDM 2005

SiC Stressor



Yeo, Semicond. Sci. Tech. 2007

Strain Transfer Structure (STS)

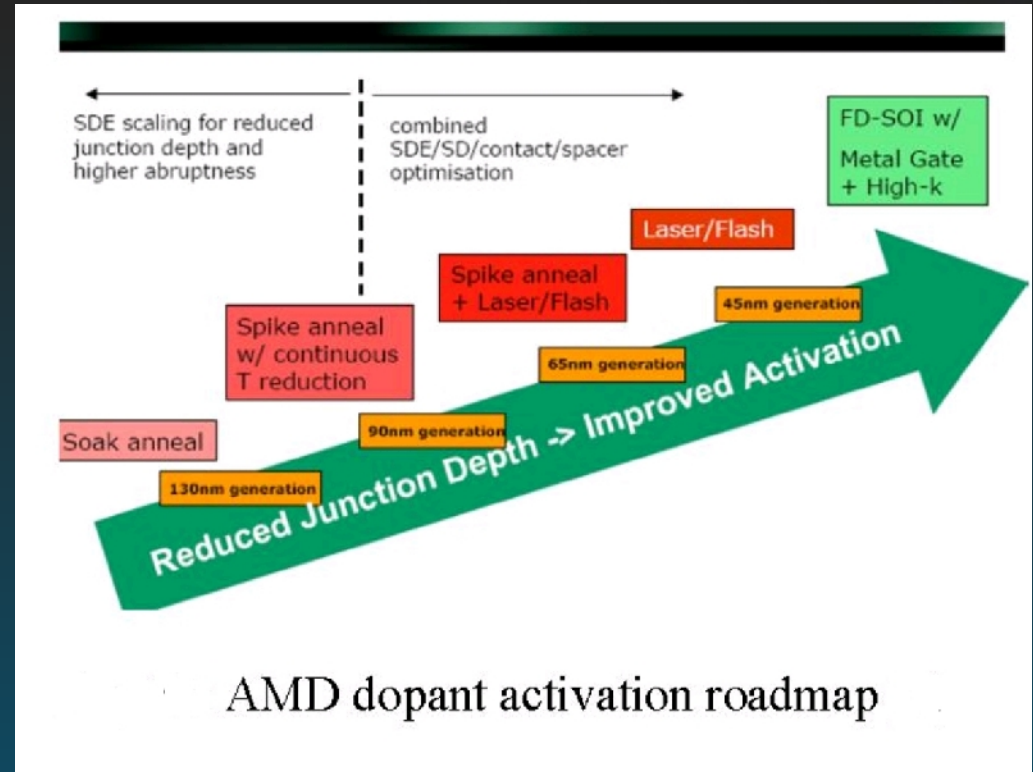
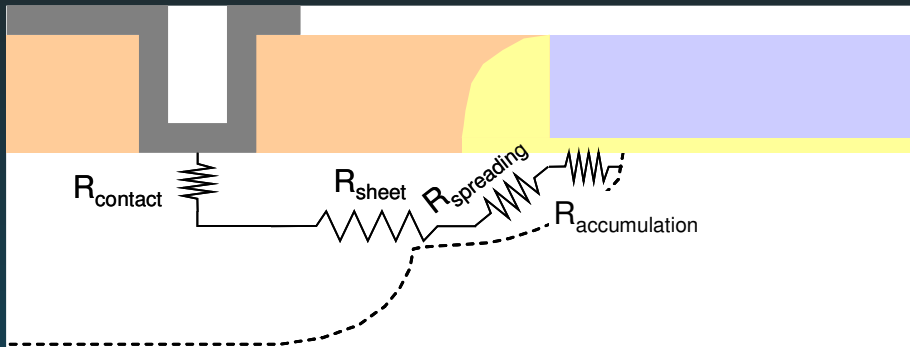


H. S. Ang et al., VLSI 2007

Level of stress in the channel



Junction optimisation



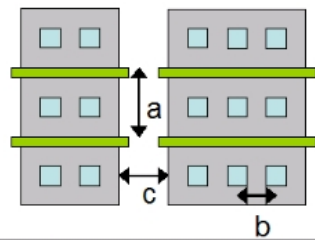
R_{Sheet} : Conductivity of high doped region
 High activation: complex techniques

J. O. Borland, « 32 nm NODE USJ Implant & Annealing, RTP 2007

Challenges for 32 & 22 nm

Challenges and Opportunities for High Performance 32 nm CMOS Technology

J.W. Sleight, I. Lauer, O. Dokumaci, D. M. Fried, D. Guo, B. Haran, S. Narasimha, C. Sheraw, D. Singh, M. Steigerwalt, X. Wang, P. Oldiges, D. Sadana, C.Y. Sung, W. Haensch, and M. Khare
 IBM T. J. Watson Research Center, 1101 Kitchawan Road, Yorktown Heights NY 10598
 sleight@us.ibm.com (914) 945-1876



	65 nm	45 nm	32 nm
(a) Gate pitch	~250 nm	180-190 nm	~130 nm
(b) Contact Pitch	195 nm	140-144 nm	~100 nm
(c) N/P Spacing	~130 nm	~102 nm	~70 nm

Fig. 1: Selected critical dimensions for different technology nodes.

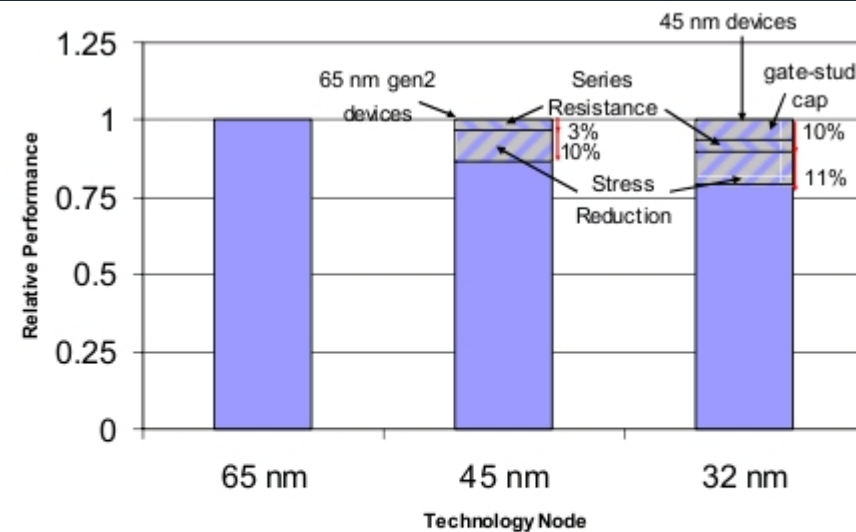


Fig. 2: Performance loss associated with pitch scaling for the 45 nm and 32 nm nodes. The performance loss associated with parasitics and stress loss is likely exacerbated at the 32 nm node.

J. W. Sleight et al., IEDM Tech. Dig., 2006

Challenges for 32 nm

- Scalability:
 - -11% stress reduction compared to 65nm (decreasing gate pitch) [Sleight06]
 - ITRS Junction target (extension depth, abruptness& sheet resistance) challenging
 - Yield:
 - ITRS[07] : integration of multiple sources of local and global stress
 - Not exceeding the local critical shear stress
 - Design
 - Pitch and layout dependent
 - *“Strain adds new challenges from a design perspective”* [Lammers08]
- TCAD have a role to play to provide key information (process => design)

PART II: Process Simulation ?



Materials Science and Engineering B 124-125 (2005) 81-85

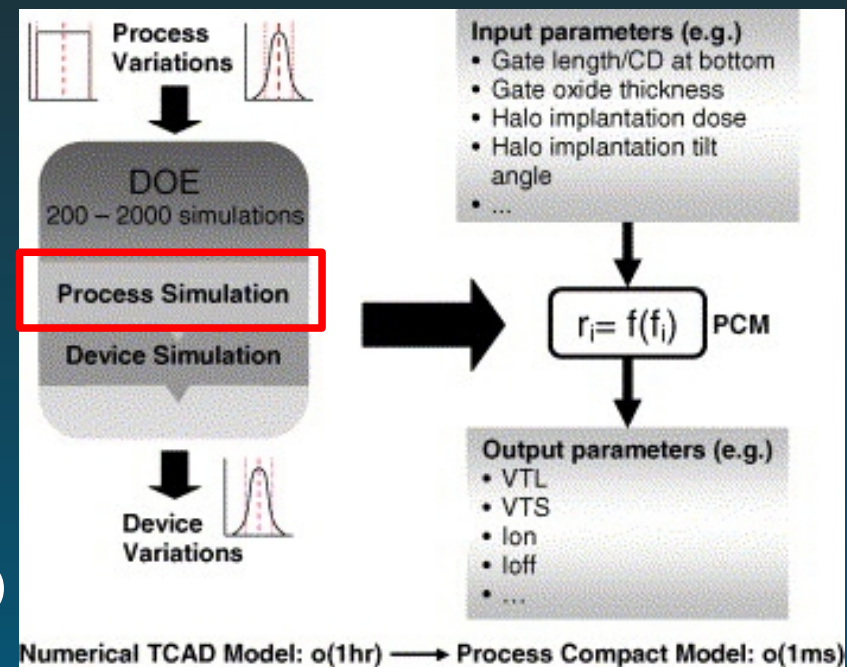
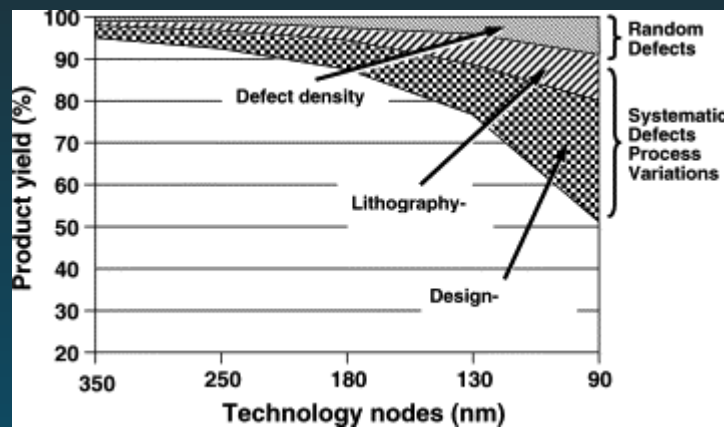
**MATERIALS
SCIENCE &
ENGINEERING
B**

www.elsevier.com/locate/mseb

Trends, demands and challenges in TCAD

Ingo Bork*, Victor Moroz, Lars Bomholt, Dipu Pramanik

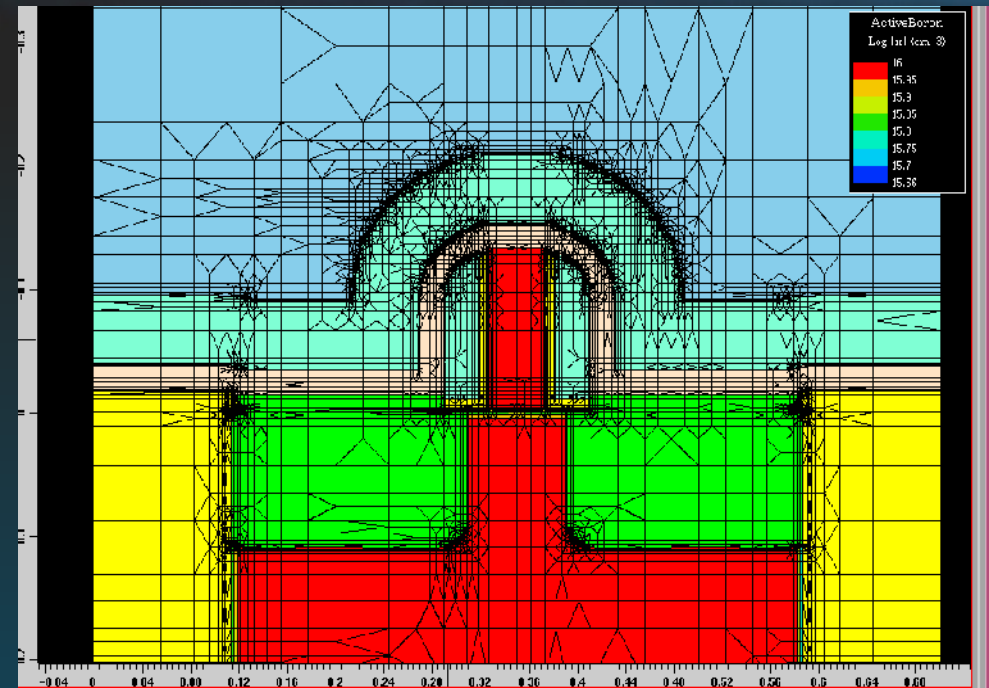
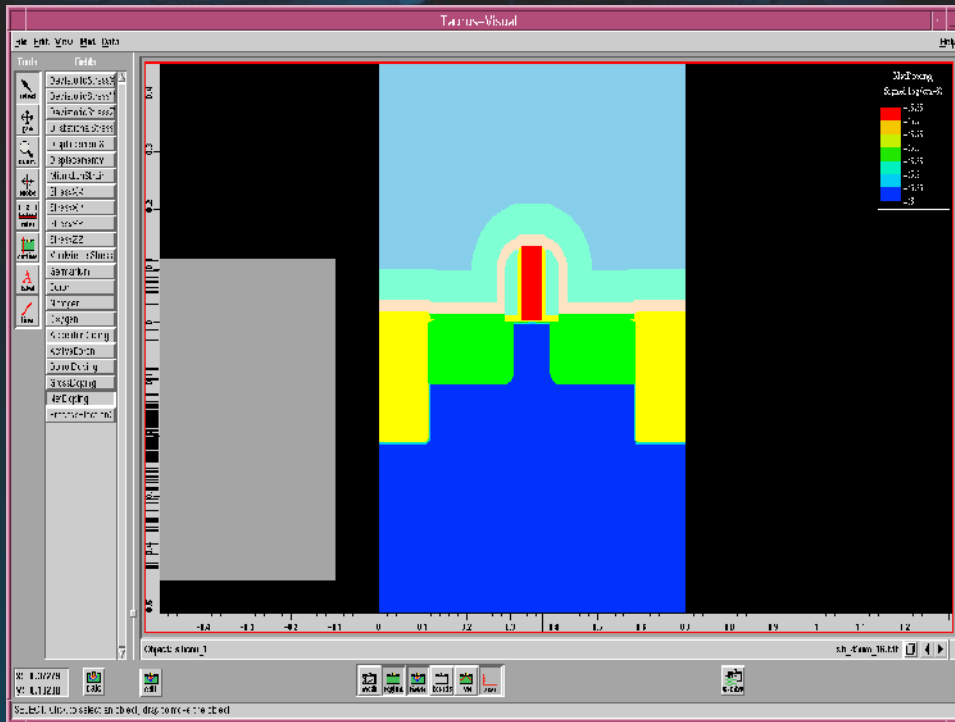
Synopsys, Inc., 700 E. Middlefield Rd., Mountain View, CA 94043, USA



TCAD :

- ↘ Technology cost development (40% ITRS)
- ↗ Yield

Process Simulation

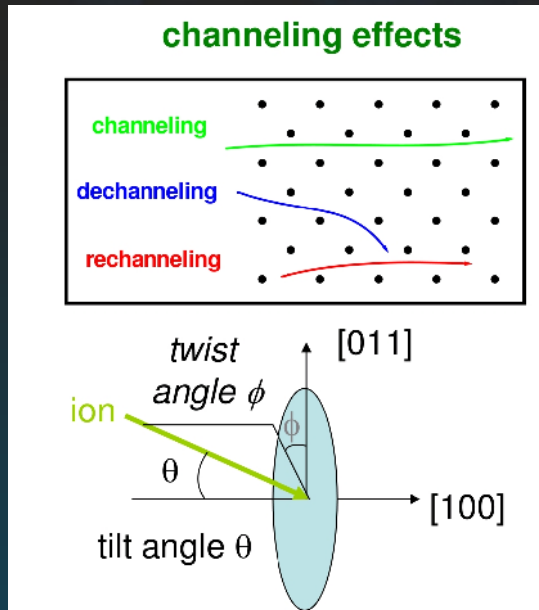


Standard process simulation:

- Transistor Building (finite elements)
- Simulation of the various process step (implantation, diffusion, oxidation, silicidation)
- « Physical » modeling with partial differential equations (PDE)
- Knowledge of the various physical parameters (topology, dopant distribution, stress field) for electrical simulation

Implantation modeling

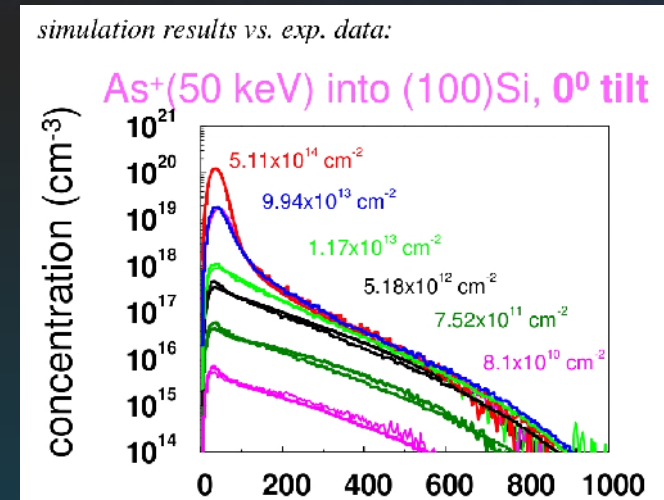
Implantation modeling : Implant tables or Monte-Carlo Simulation



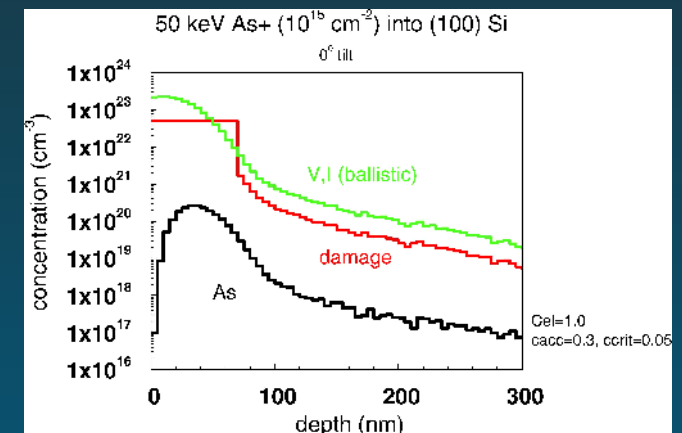
Series of consecutive binary collisions of the projectile with the lattice (BCA MC):

- Nuclear scattering (Coulomb pair potential)
- Semi empirical model for the electronic energy loss of particles
- Phenomenological models for damage probability

M. Posselt, private communication



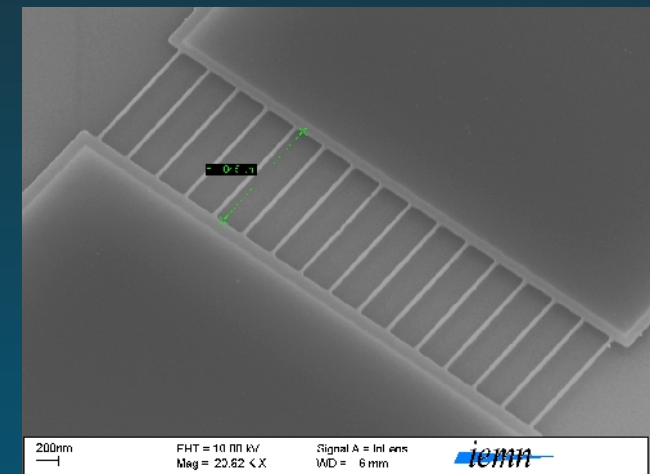
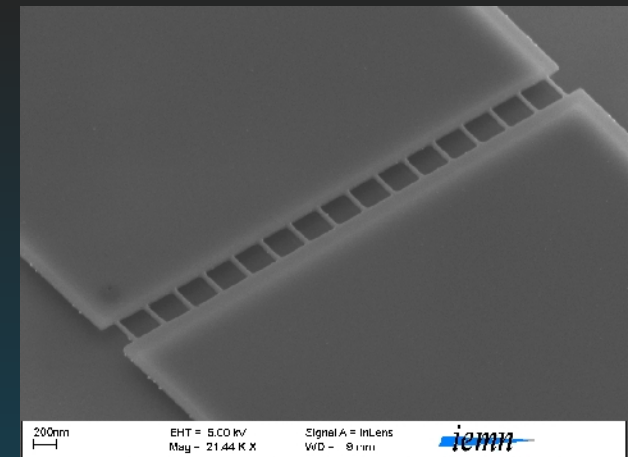
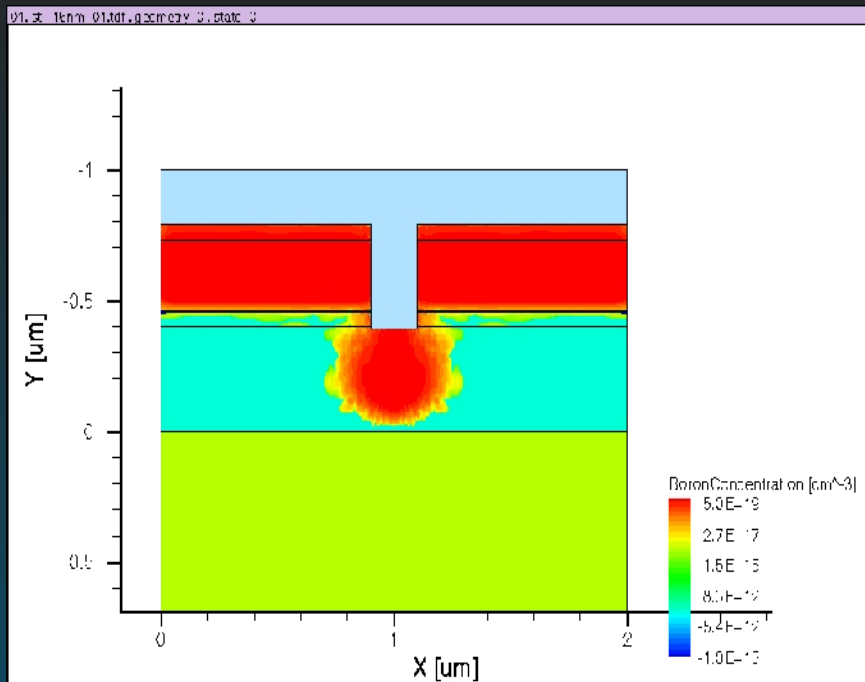
Range distribution of implanted ions



Damage profile

Implantation Modeling Example

- 2D Implant modeling for nanowire fabrication



Creation of Silicon nanowire by anisotropic etching with a damage gradient
Optimisation (Dopant, Dose, Energy) with simulation

Vikram Passi et al., UCL, NANOSIL WP 2.1 (unpublished results)

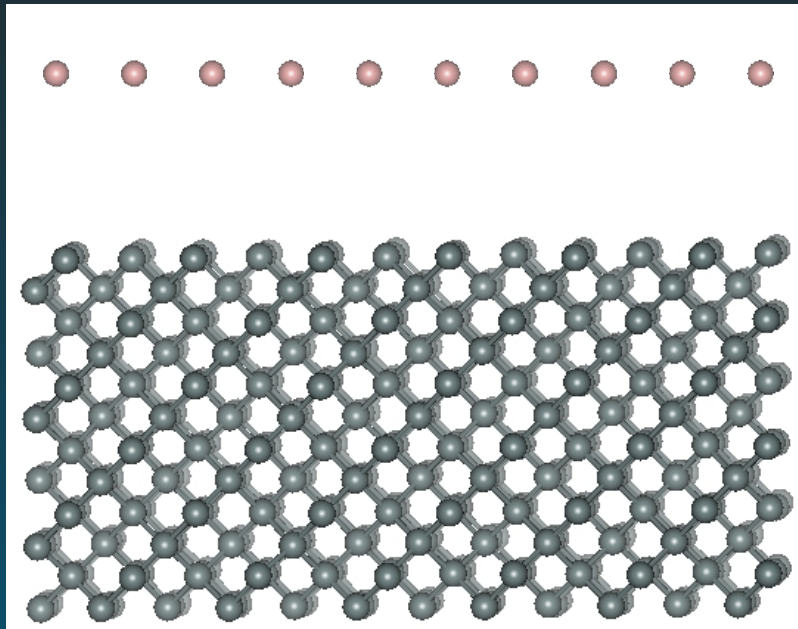
Diffusion modeling (1)

Junction Fabrication

Standard Technology

Ionic implantation for the dopant with various energy & dose

Boron atoms



After implantation:

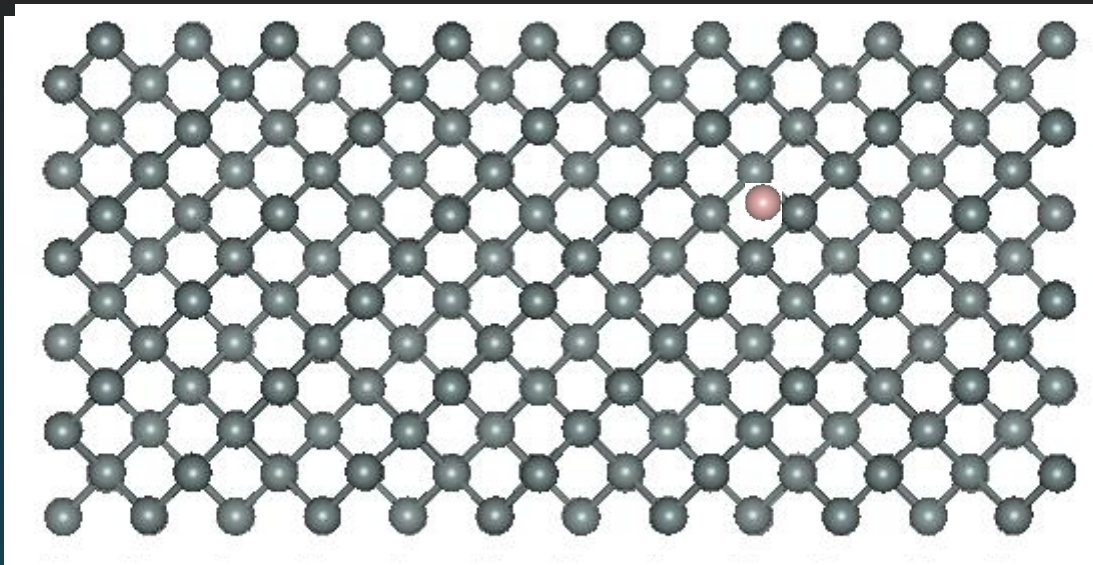
- Dopants in an interstitial position electrically inactive
- Defects created : interstitials, vacancies, aggregate, amorphous pocket

→ Annealing step mandatory

Diffusion Modeling (2)

Boron Kick-out

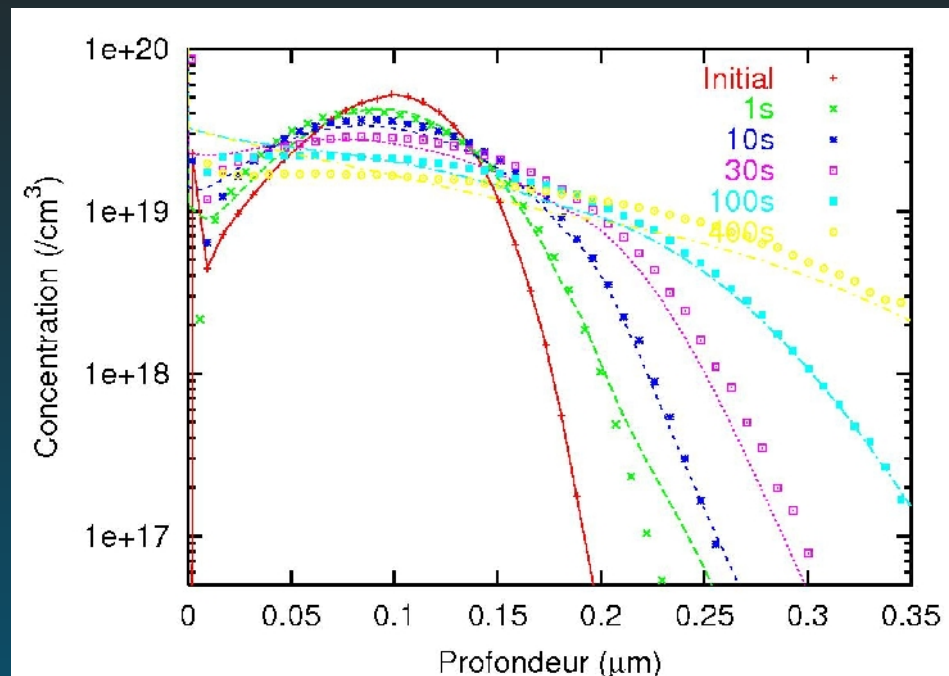
What's going on during annealing? Example for boron



- Interstitial Boron mobile form
- Immobile Boron impurity (electrically active) and creation of Si interstitial
- Diffusion and recombinaison of Si interstitial.
- Kick-out of a boron atoms by an another Si interstitial
- ...
- The junction depth and the activated dose results from the contribution of all these mechanisms
- Standard process simulator used Fick law and diffusion- reaction equations to describe the the intreaction with point defects and mechanism like kick-out

Diffusion Modeling (3)

- Application: Evolution of doping profile during annealing critical for electrical properties (see also slide 44)



Example of Boron diffusion profile diffusion

Oxidation and stress modeling (1)

JOURNAL OF APPLIED PHYSICS

VOLUME 36, NUMBER 12

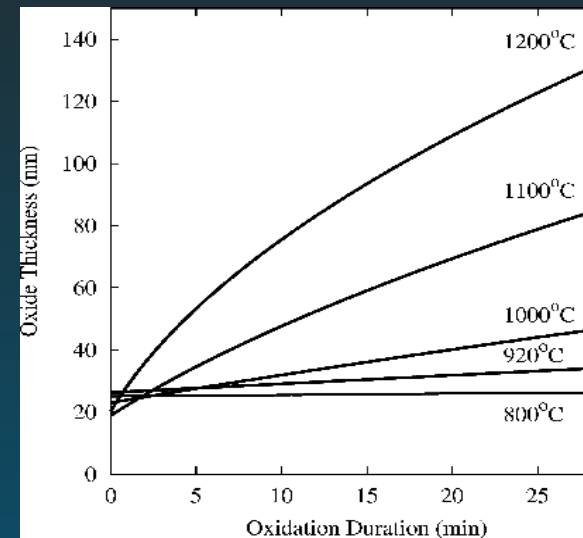
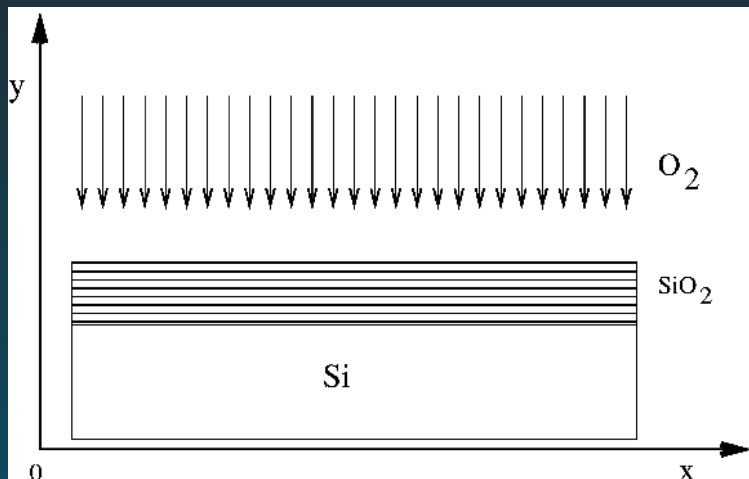
DECEMBER 1965

General Relationship for the Thermal Oxidation of Silicon

B. E. DEAL AND A. S. GROVE

*Fairchild Semiconductor, A Division of Fairchild Camera and Instrument Corporation,
Palo Alto, California*

(Received 10 May 1965; in final form 9 September 1965)

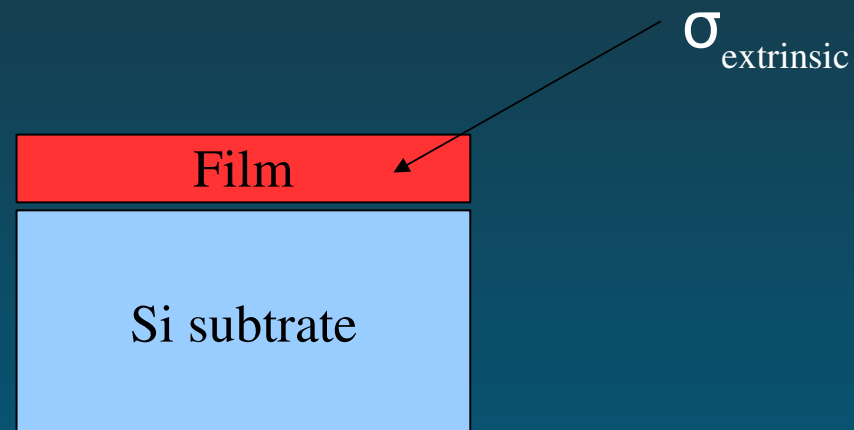


Process simulator : generalised Deal & Grove oxidation model (diffusivity & reaction rate stress-dependent) to take into account the stress (volume expansion)

Various source of stress

Stress sources	Technical Process
Thermal Stress	Thermal variation during various processing step
Topological induced Stress	Thermal growth (oxidation, silicidation), etching
Intrinsic Stress	Film deposition process (nitride, polysilicon, metals....)
Extrinsic stress	Structural modifications of films
High doping induced stress	Steep doping gradients

Example : modeling of stress generated by deposition of thin film
introduction of an extrinsic stress and mechanical equilibration



Example: Oxidation and stress modeling

JOURNAL OF APPLIED PHYSICS

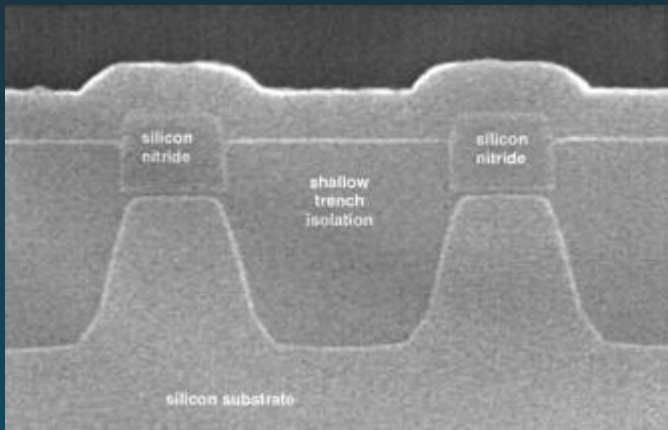
VOLUME 94, NUMBER 9

1 NOVEMBER 2003

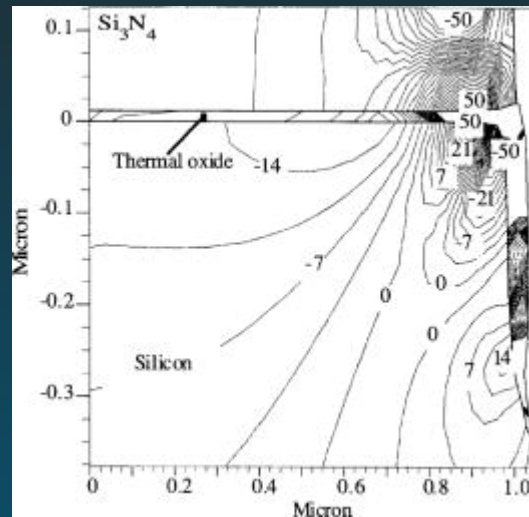
Strain determination in silicon microstructures by combined convergent beam electron diffraction, process simulation, and micro-Raman spectroscopy

Vincent Senez^{a)}

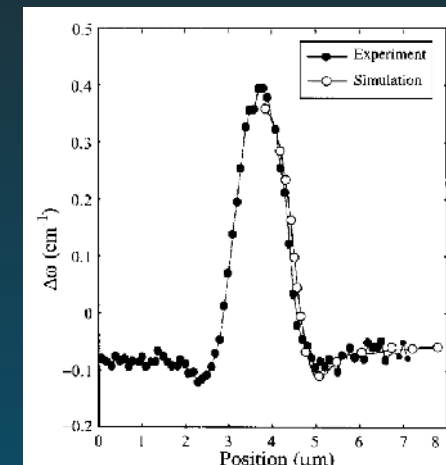
IEMN-ISEN, UMR CNRS-8520, Avenue Poincaré, B.P. 69, 59652 Villeneuve d'Ascq cédex, France



STI (Shallow stress Isolation structure)



Stress field (TCAD)



μRS (experiment vs simulation)

but for Large structure

Conclusion

- These different examples => process modeling promising
- Reality is/was more complex (2002)
 - Example taken from different or academic softwares
 - Difficulty to describe TED Boron, segregation effects, ultra-thin oxidation, silicidation....
 - No real stress modeling capabilities (commercial tool)
- The Mark Law definition: « **TCAD : yesterday's technology modeled tomorrow** »

Process
modeling
for future
technologies

by M. E. Law

M. E. Law, IBM J. Res. Dev., Vol. 46, n°2/3, March 2002

Conclusion

- « **TCAD : yesterday's technology modeled tomorrow** » still true ?
- No:
 - Large progress have been performed in diffusion modeling (Support by the EC: European project Rapid, Frenotech, PullNaNo,Atomics)
 - Progress have been done for « simple » stress modeling
 - The merging of the major TCAD firms (Avant!, ISE, Synopsys) ~ market 80%
DIOS (meshing, numerical stability), TAURUS (3D capabilities, Implantation, stress) and TSUPREM-IV (oxidation modeling) to the FLOOPS-ISE (new diffusion modeling)
 - More contribution and more insight with atomistic modeling
 - There is also a part of « dream »: simulation can not replace characterisation
 - Script models speed up the pipeline (M. Law) : University (models)=>TCAD company (software) => Semiconductor Company ? No but more
- Yes:
 - Complexity increase : Stress Engineering (Slide 8), New material (Ge), Laser Annealing & Solid Phase Epitaxy.....

Recent progress in the modeling of stress

Modeling SiGe S/D stress field

APPLIED PHYSICS LETTERS 86, 023103 (2005)

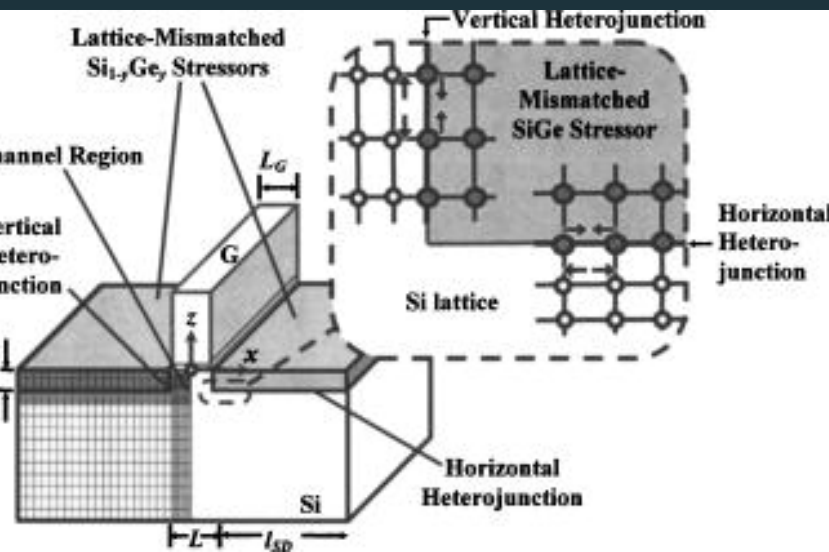
Finite-element study of strain distribution in transistor with silicon-germanium source and drain regions

Yee-Chia Yeo^{a)}

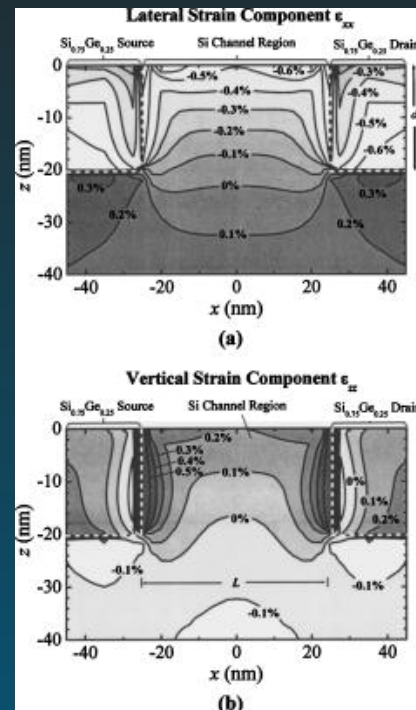
Silicon Nano Device Laboratory, Department of Electrical and Computer Engineering, National University of Singapore, 119260, Singapore

Jisong Sun

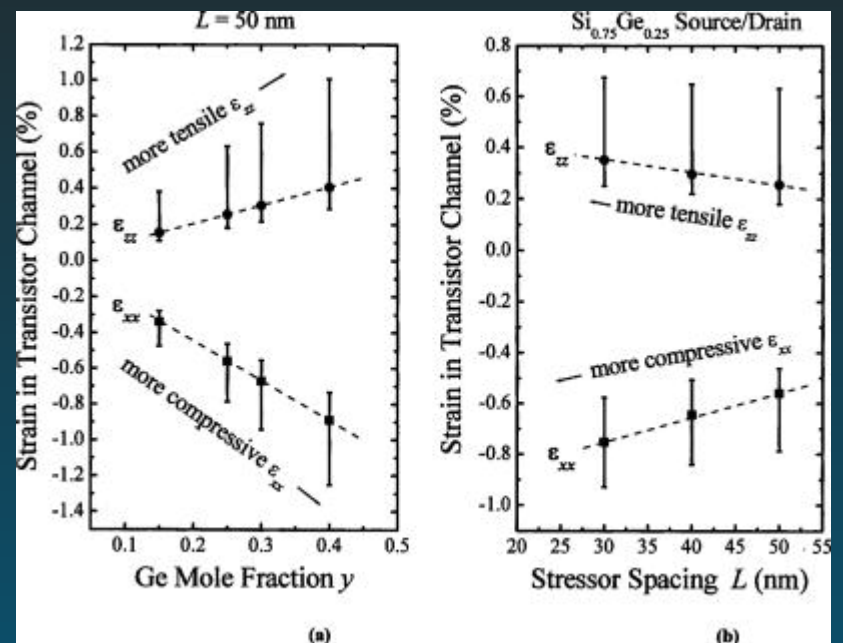
Agency for Science, Technology, and Research, Data Storage Institute, DSI Building, 5, Engineering Drive 1, 117608, Singapore



Principle of Lattice-mismatched stressor



Lateral & Vertical strain induced



Evolution of channel strain as a function of the Ge fraction and the spacer with

Y. Yeo et al., *Appl. Phys. Lett.*, 86, 023103, 2005

SiGe S/D scalability

IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 53, NO. 7, JULY 2006

1617

Scalability of the $\text{Si}_{1-x}\text{Ge}_x$ Source/Drain Technology for the 45-nm Technology Node and Beyond

Geert Eneman, Peter Verheyen, Rita Rooyackers, Faran Nouri, *Senior Member, IEEE*, Lori Washington, Robert Schreutelkamp, Victor Moroz, Lee Smith, *Member, IEEE*, An De Keersgieter, Malgorzata Jurczak, and Kristin De Meyer, *Senior Member, IEEE*

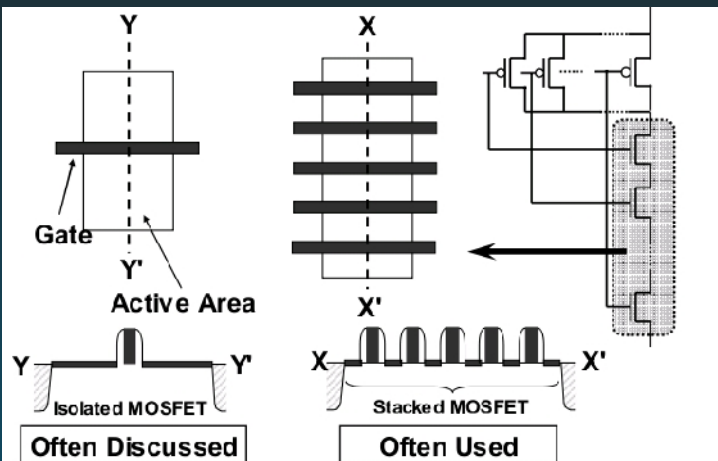
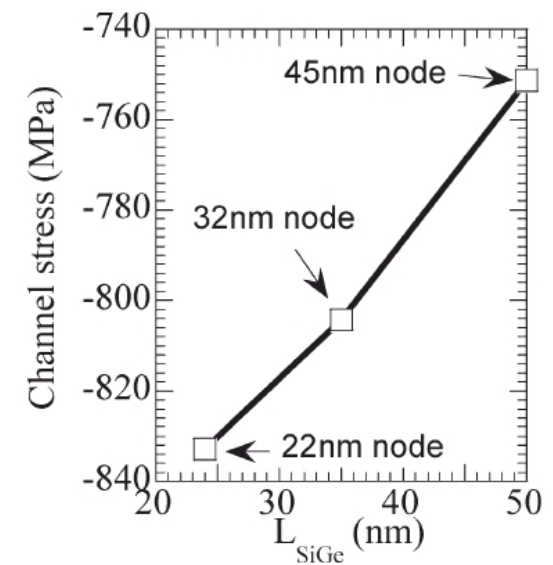
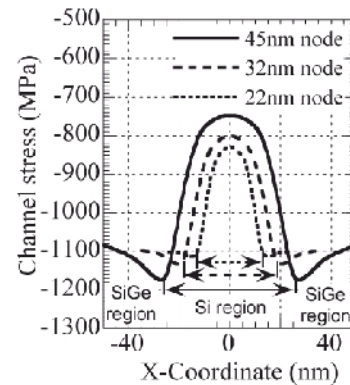


Fig.1 Schematic view of MOSFET layout which is often used and often discussed. Stacked MOSFET which is often used in actual products should be discussed.

TABLE I
TECHNOLOGY PARAMETERS FOR THE 45-, 32-, AND 22-nm TECHNOLOGY NODE

	$L_g(\text{nm})$	$L_{sd}(\text{nm})$	$L_{\text{SiGe}}(\text{nm})$	$t_{\text{SiGe}}(\text{nm})$	$W(\text{nm})$
45nm node	18	100	50	60	100
32nm node	13	70	35	50	70
22nm node	9	50	24	45	50



Mean compressive channel stress does not decrease with downscaling

G. Eneman et al., *IEEE Trans. on Electron Device*, Vol. 86, 023103, 2005

Modeling CESL stress

Multi-Layer Model for Stressor Film Deposition

K.V. Loiko, V. Adams, D. Tekleab, B. Winstead, X.-Z. Bo, P. Grudowski, S. Goktepe, S. Filipiak, B. Goolsby, V. Kolagunta, and M.C. Foisy

Austin Silicon Technology Solutions, Freescale Semiconductor, Inc.
3501 Ed Bluestein Blvd, Austin, TX 78721
Email: loiko@freescale.com

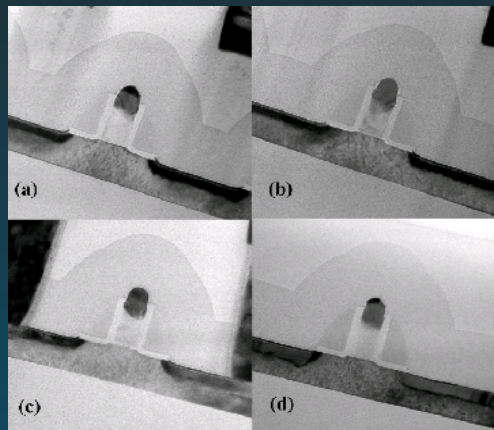


Figure 1. TEMs of 35nm gates with highly stressed ESL films as a function of gate poly pitch: (a) 0.26 μm , (b) 0.38 μm , (c) 0.63 μm , (d) 1.04 μm .

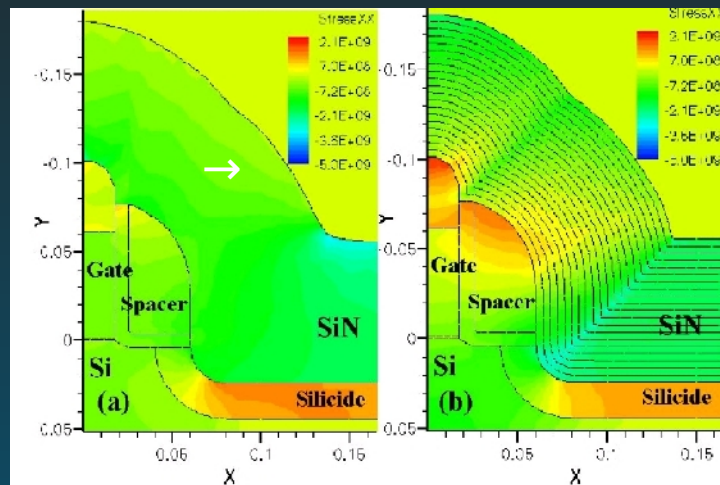


Figure 7. Contours of lateral stress (Pa) in 35nm transistor structures with 20nm source/drain recess simulated using (a) single-layer and (b) 20-layer deposition of nitride with compressive intrinsic stress.

Large difference between mono and multi step deposition

K. V. Loiko et al., SISPAD 2006

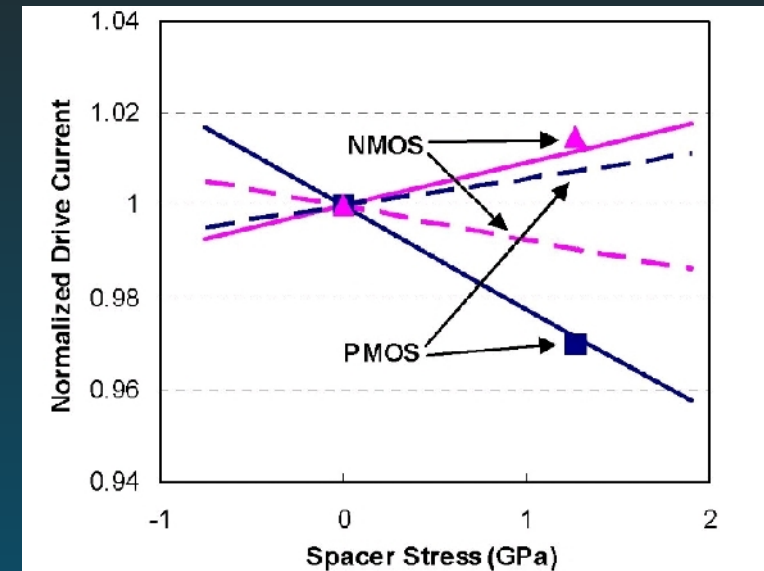


Figure 8. Experimental data (symbols), multi-layer (solid lines) and single-layer (dashed lines) simulation results on NMOS (lensile ESL) and PMOS (compressive ESL) drive current vs. spacer stress.

Opposite experimental trends with mono step deposition !

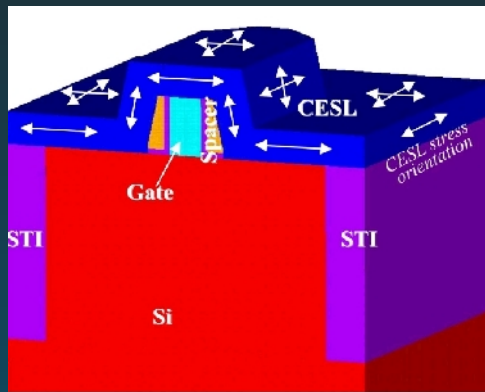
Engineering the CESL stress

814

IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 54, NO. 4, APRIL 2007

Method for Managing the Stress Due to the Strained Nitride Capping Layer in MOS Transistors

Stéphane Orain, Vincent Fiori, Davy Villanueva, Alexandre Dray, and Claude Ortolland



3D Ansys Simulation

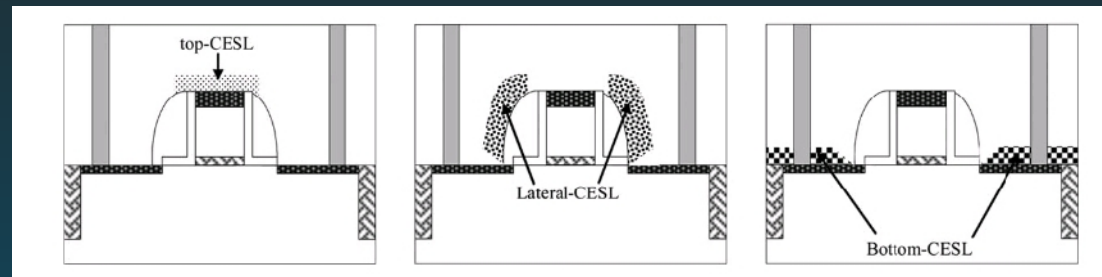


TABLE I
SUMMING UP THE IMPACT OF ALL THE CESL EFFECTS (C = CORNER, D = DIRECT, AND I = INDIRECT) FOR EACH CESL ZONE (TOP, LAT. = LATERAL, AND BOT. = BOTTOM)

		Corner	Top	Lat.	Bot.	LEGEND:
Long	Sx	C ⁺	D ⁻	0	D ⁺	C : Corner effects
	Sy	C ⁺	D ⁻	0	D ⁺	D : Direct effects
	Sz	0	I ⁻ /D ⁻	0	0	I : Indirect effects
Short	Sx	C ⁺	0	D ⁻	D ⁺	- : Compressive stress
	Sy	C ⁺	0	D ⁻	D ⁺	+ : tensile
	Sz	0	I ⁻	I ⁻ /D ⁻	D ⁻	0 : no or low impact

Which part of the CESL influence the channel stress ?

- Complex answer (Long<>short device) !
- Such table provide guidelines for device optimisation
- Geometry of the spacer (L or D shape) important

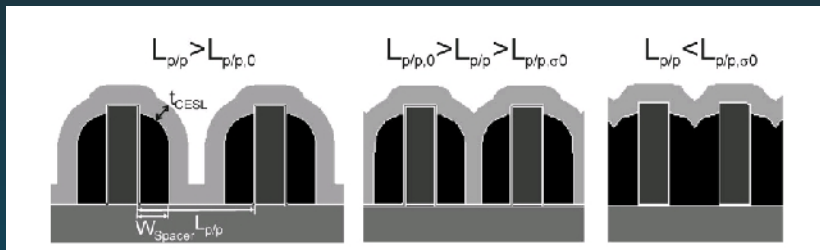
Scalability of CESL

1446

IEEE TRANSACTIONS ON ELECTRON DEVICES, VOL. 54, NO. 6, JUNE 2007

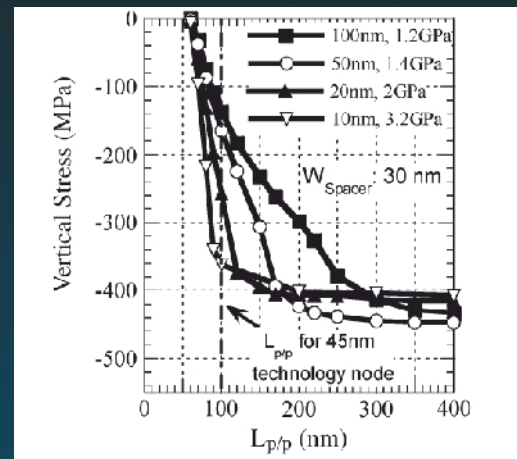
Scalability of Stress Induced by Contact-Etch-Stop Layers: A Simulation Study

Geert Eneman, Peter Verheyen, An De Keersgieter, Malgorzata Jurczak, and Kristin De Meyer, *Senior Member, IEEE*

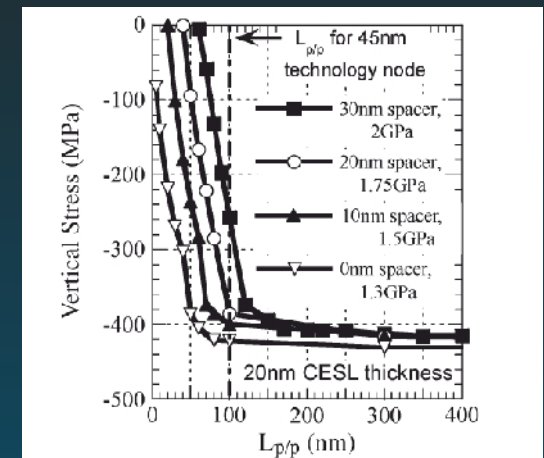


Poly to Poly Distance: $L_{p/p}$

$$L_{p/p} > L_{p/p,0} = 2 \cdot t_{CESL} + 2 \cdot W_{Spacer}$$



For large CESL thickness, decreasing $L_{p/p}$ leads to stress reduction

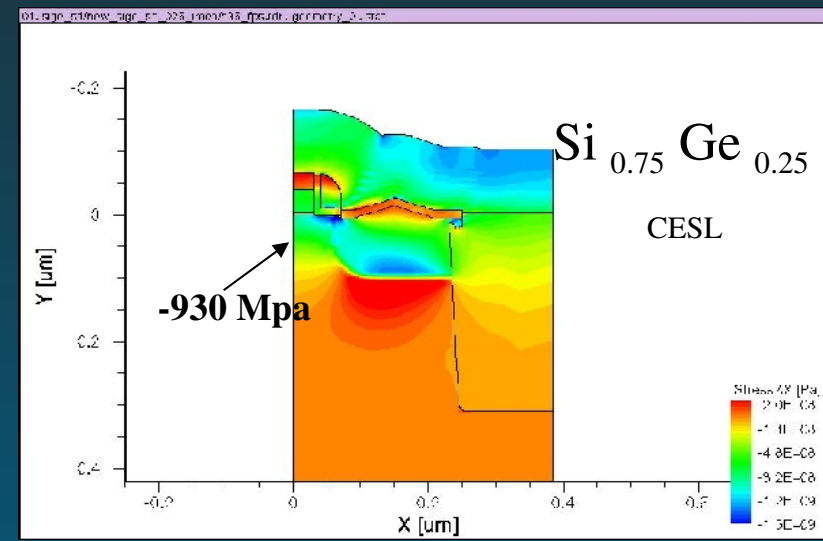
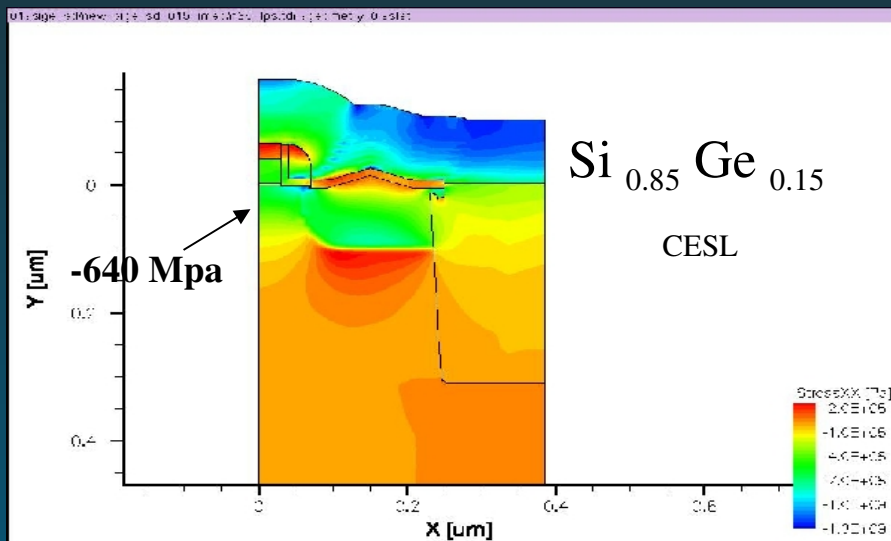
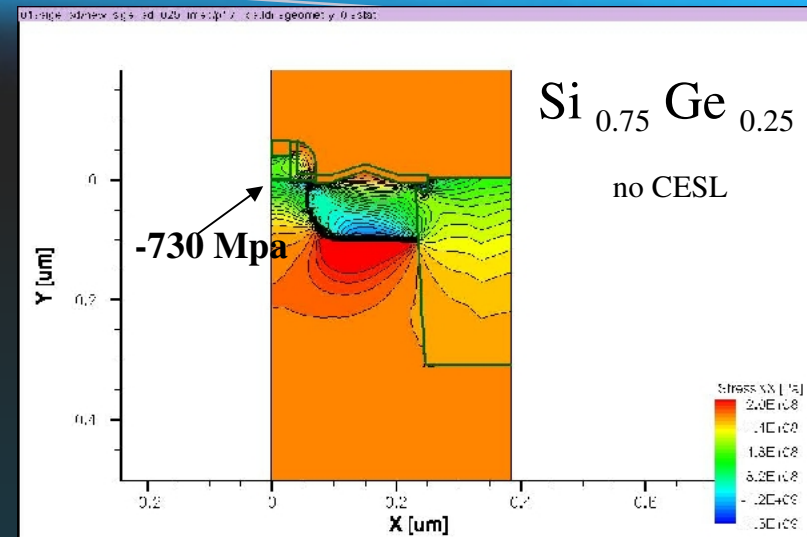
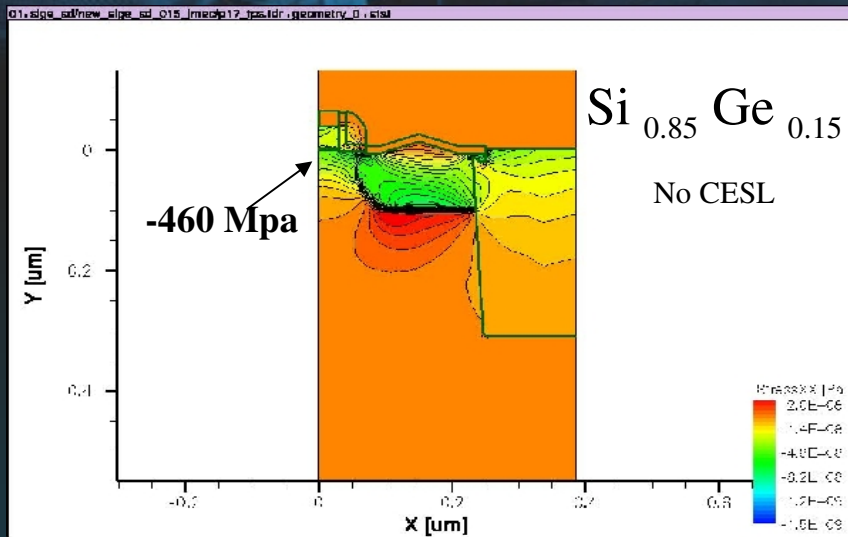


Influence of spacer width on vertical stress for decreasing $L_{p/p}$

↘ CESL thickness is no sufficient, spacer dimensions must be scaled

G. Eneman et al., *IEEE Trans. on Electron Device*, Vol. 54, N°6, June, 2007

S/D SiGe & CESL modeling with SProcess



C. Krzeminski, PULLNANO Results (unpublished)

Conclusion

- Large progress have been performed in the stress modeling with the support of experimental development, study of topography influence, evaluation of scalability (SiGe S/D or Stress Liner)
- There was one issue :

Journal or major proceedings conferences Publications (2001-2008)	Number	Proprietary simulator	“Old” simulator Taurus/ Tsuprem-IV	Mechanical simulator (Ansys/ FEMLAB)	Sentaurus Process
TCAD&stress	14	30%	40%	30%	0%

- But large progress have been performed recently in the last version of Sentaurus Process as shown by the last PullNANO Results
- Still a lot of work: Stress Memorization, SiC stressor.....

Progress in diffusion modeling

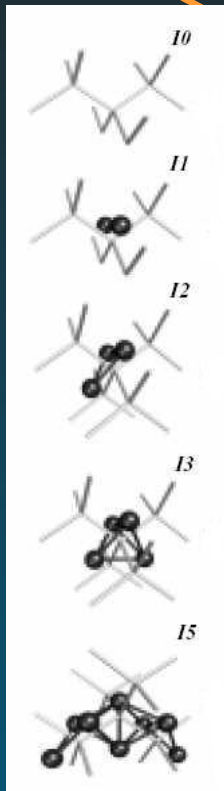
Extended defects

Role on extended defects formed after ion implantation of dopants

2 atoms

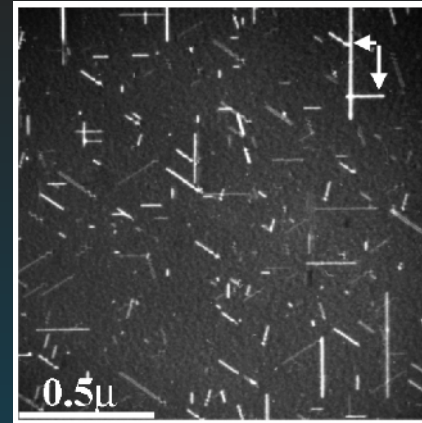
Small clusters

Bongiorno, Europhys. Lett. 50, 608 (2000).



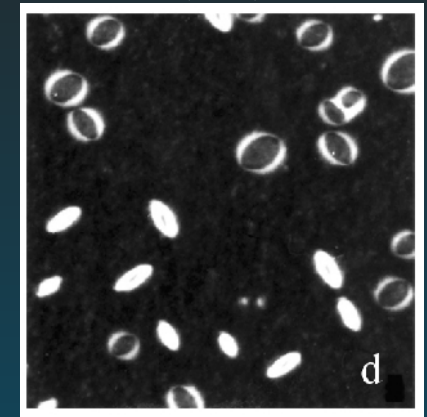
{113} defects

Cherkashin, MRS Symp. Proc. 810, C3.7 (2004).

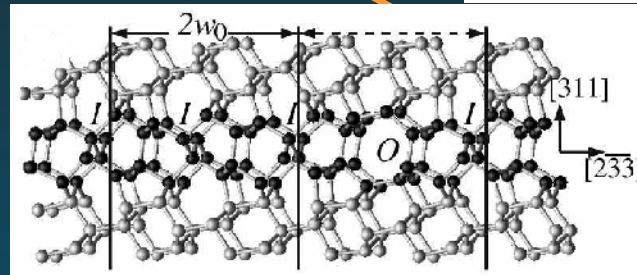


CEMES/LAAS

Claverie, MRS Symp. Proc. 610, B11.6 (2000).

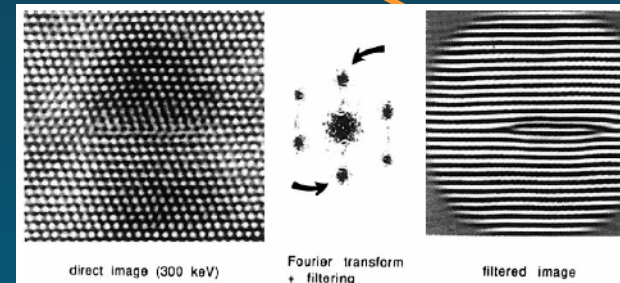


Dislocation loops



Kim, Phys. Rev. Lett. 84, 503 (2000).

Claverie, Mat. Sc. Semicond. Proc. 3, 269 (2000).

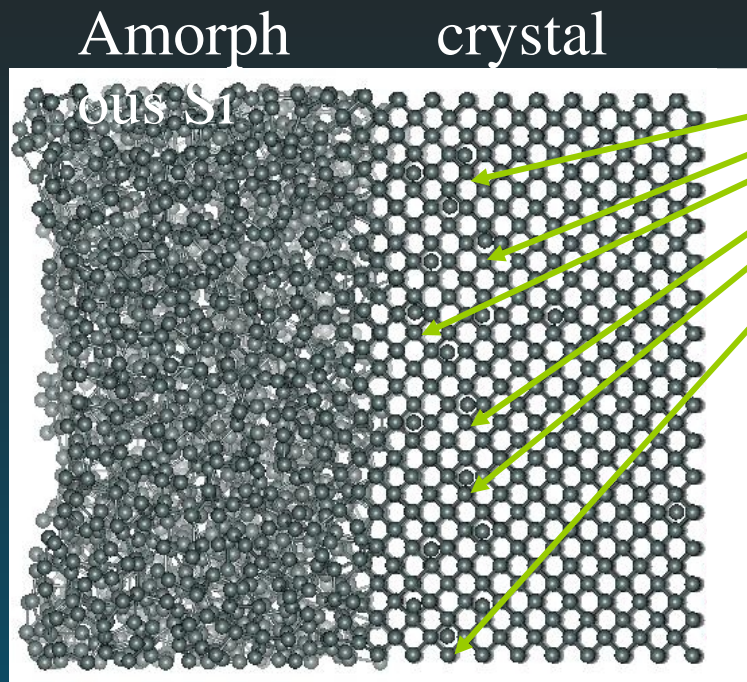


~ 10000 atoms

Boron Transient enhanced diffusion (TED) & extended defects

→ Common origin : the supersaturation of interstitials formed by the implantation step

Ex in the case of a preamorphisation :



Excess or supersaturation of interstitials just behind the amorphous /cristalline interface

During annealing :

Precipitation into extended defects

Accelerated diffusion of boron

→ Need to couple a model of extended defects to conventionnal packages of dopant diffusion

nucleation, pure growth and Ostwald ripening of defects

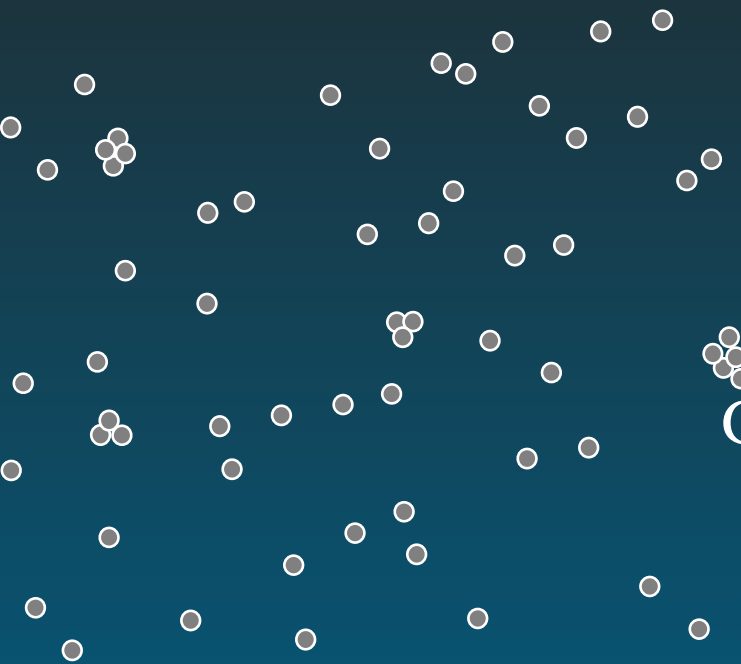
- Nucleation of extended defects – reduction of the system energy



nucleation, pure growth and Ostwald ripening of defects

- Nucleation of extended defects – reduction of the system energy
- Growth of the nuclei by absorption of the residual interstitials

→ pure growth

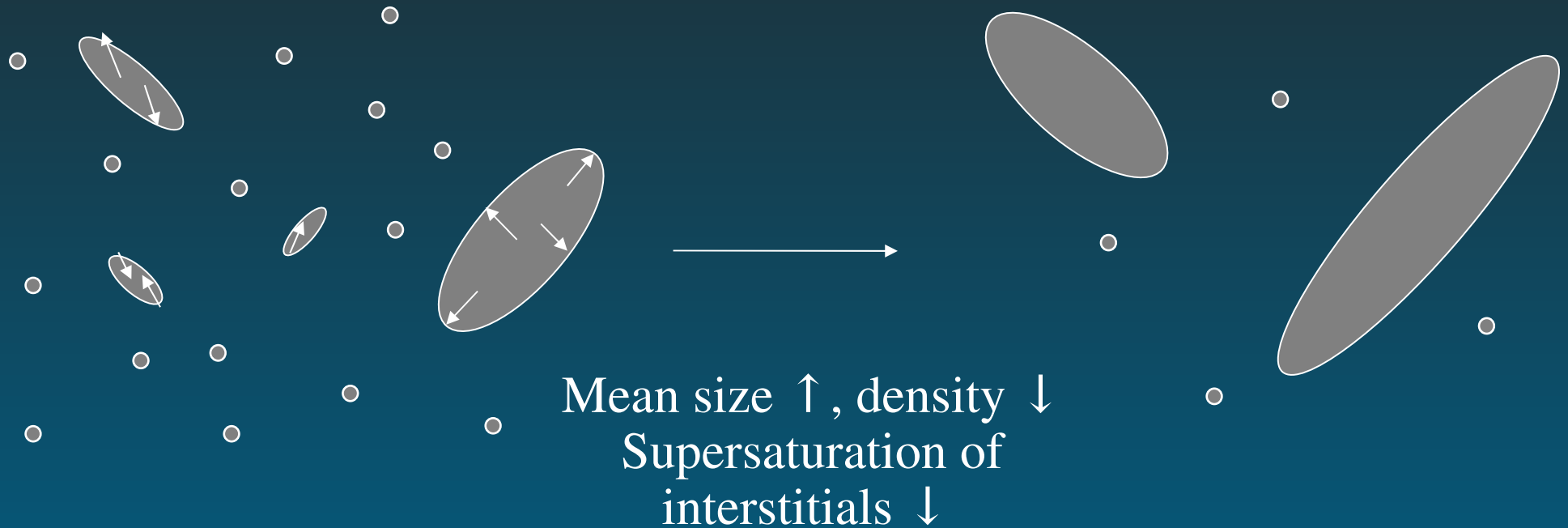


Growth of the existing defects
Supersaturation ↓



Nucleation, pure growth and Ostwald ripening of defects

- Nucleation of extended defects – reduction of the system energy
- Growth of the nuclei by absorption of the residual interstitials
→ pure growth
- Ostwald ripening (dynamical equilibrium) extended defects ↔ interstitial supersaturation



TED and Dislocation Loops (DL)

JOURNAL OF APPLIED PHYSICS

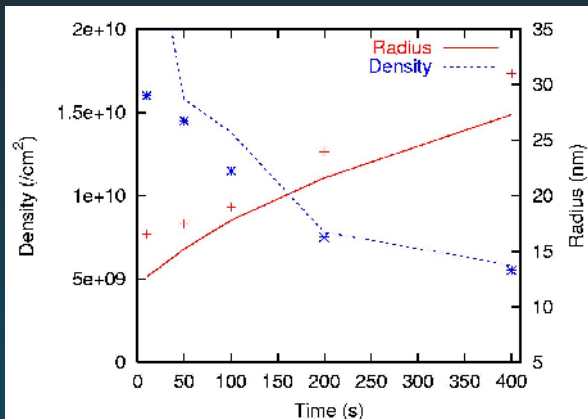
VOLUME 85, NUMBER 12

15 JUNE 1999

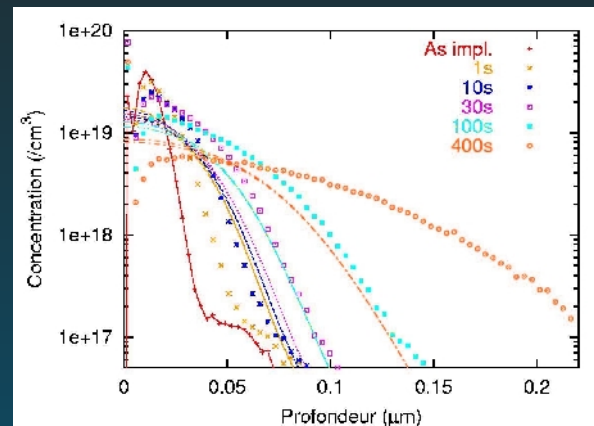
Modeling of the transient enhanced diffusion of boron implanted into preamorphized silicon

E. Lampin^{a)} and V. Senez
IEMN-Dpt. ISEN, UMR CNRS 9929, BP 69, 59652 Villeneuve d'Ascq Cédex, France

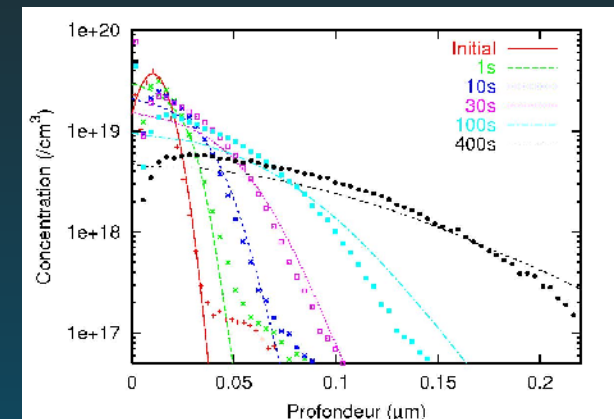
A. Claverie
CEMES-CNRS, BP 4347, 31055 Toulouse Cédex, France



Evolution of density and size of Dislocations loops (DL)



Final TED diffusion effects underestimated if DL not considered



Good predictivity of TED effects with the incorporation of DL and Si interstitials evolution

Atom-by-atom model of defects evolution

Appl. Phys. A 76, 1025–1033 (2003)
DOI: 10.1007/s00339-002-1944-0

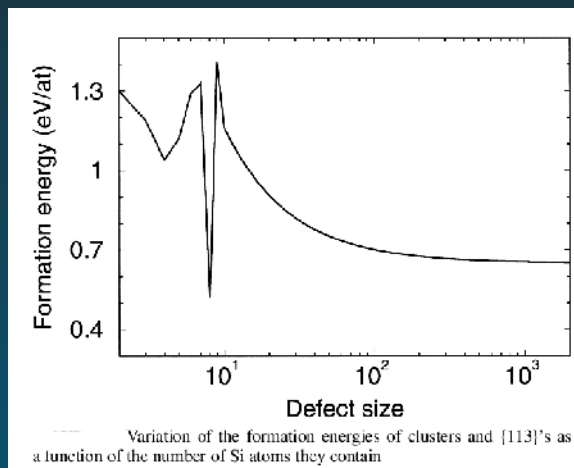
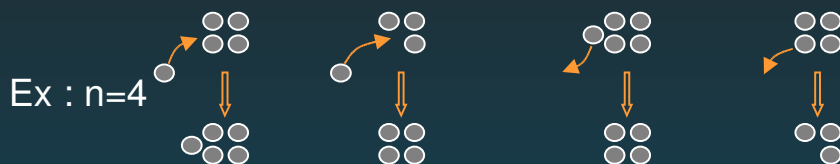
Applied Physics A
Materials Science & Processing

A. CLAVERIE^{1,✉}
B. COLOMBEAU¹
B. DE MAUDUIT¹
C. BONAFOS¹
X. HEBRAS^{1,2}
G. BEN ASSAYAG¹
F. CRISTIANO²

Extended defects in shallow implants

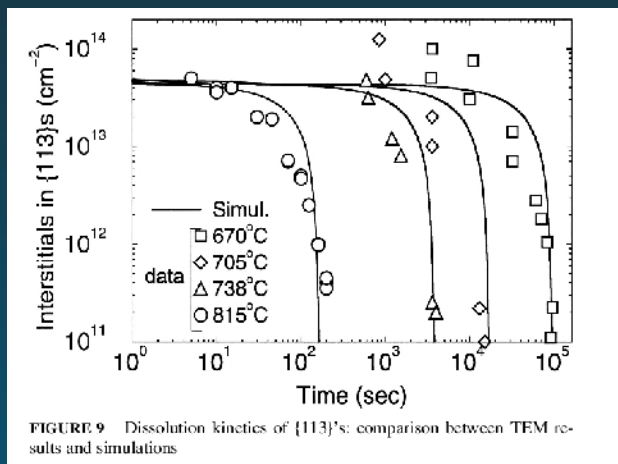
¹ Ion Implantation Group CNRS Toulouse, CEMES/CNRS, BP 4347, 31055 Toulouse Cedex, France
² Ion Implantation Group CNRS Toulouse, LAAS/CNRS, 7 Ave. Colonel Roche, 31055 Toulouse Cedex, France

$$\frac{dN_n}{dt} = -[F_n N_n - F_{n-1} N_{n-1}] + R_{n+1} N_{n+1} - R_n N_n$$

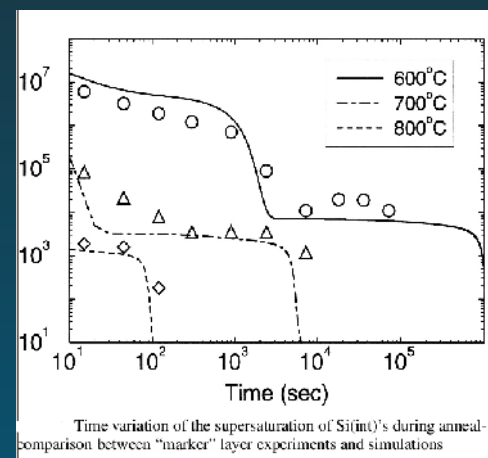


Formation energies for clusters, {113} Cowern et al.

A. Claverie et al., Appl. Phys. A, Vol. 76, 2003 (Frendtech results)



Dissolution of {113}'s



Evolution of Si interstitials as a function of the time

Coupling atom-by-atom model & diffusion

JOURNAL OF APPLIED PHYSICS

VOLUME 94, NUMBER 12

15 DECEMBER 2003

Prediction of boron transient enhanced diffusion through the atom-by-atom modeling of extended defects

E. Lampin^{a)}

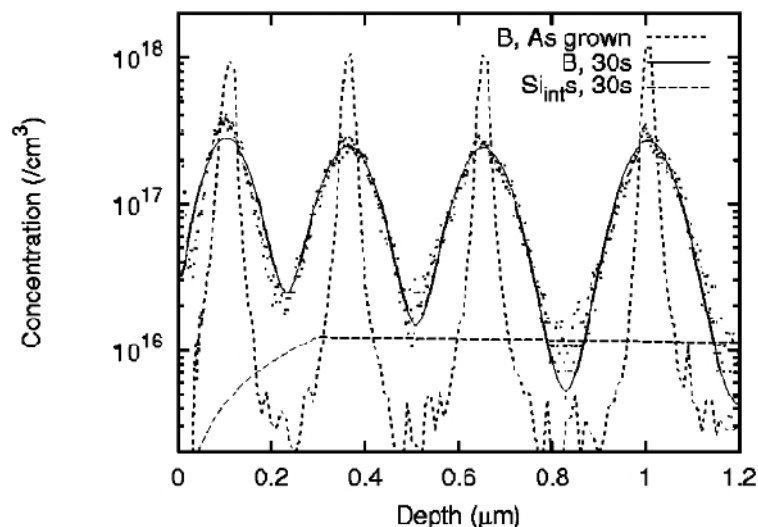
IEMN/ISEN, UMR CNRS 8520, 59652 Villeneuve d'Ascq, Cedex, France

F. Cristiano, Y. Lamrani, and A. Claverie

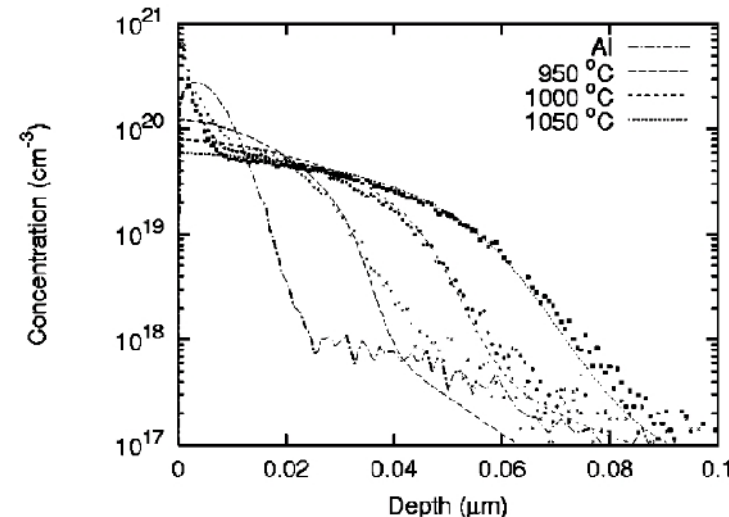
Ion Implantation Group, CEMES/LAAS-CNRS, 31055 Toulouse, France

B. Colombeau and N. E. B. Cowern

Advanced Technology Institute, University of Surrey, Guildford, GU2 7XH Surrey, United Kingdom



Nice simulation of TED effects for marked layers experiments



Nice simulation of TED for ultra-low Energy B+ implant

However, simplified model for Sprocess needed

E. Lampin et al., J. App. Phys., Vol 94, n°12, 2003 (Frendtech results)

Advanced annealing schemes

On a Computationally Efficient Approach to Boron-Interstitial Clustering

Johann Schermer and Peter Pichler
 Fraunhofer-Institute of Integrated Systems and
 Device Technology, Erlangen, Germany

Christoph Zechner
 Synopsys Switzerland LLC
 Zurich, Switzerland

Wilfried Lerch and Silke Paul
 Mattson Thermal Products GmbH
 Dornstadt, Germany

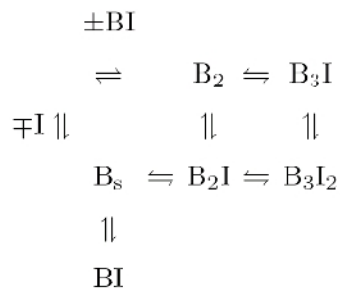


Figure 1: Scheme of reactions for the BICs model

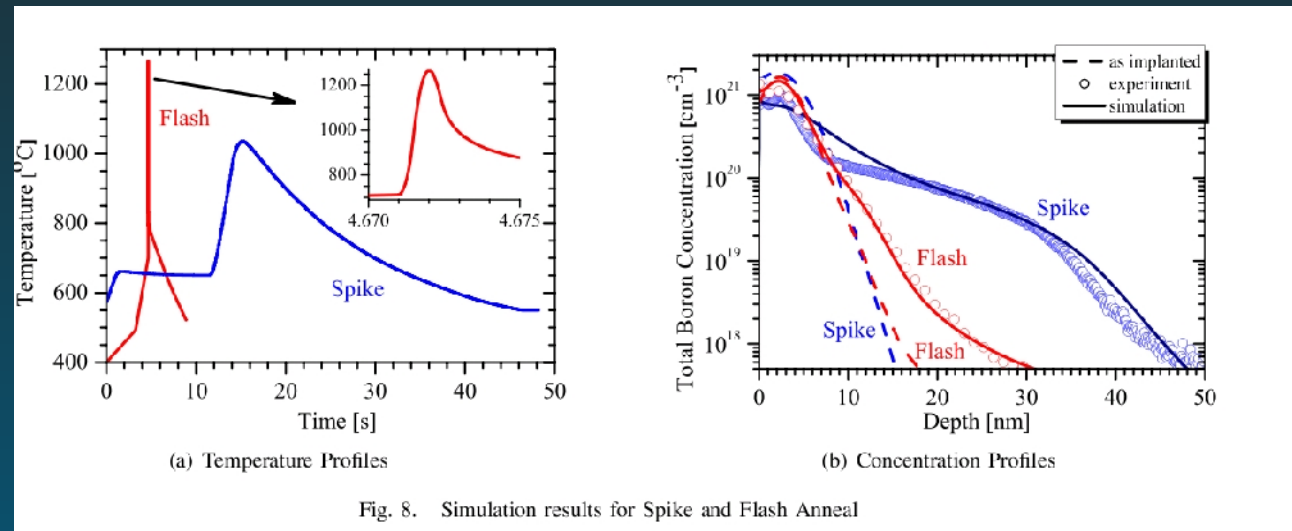
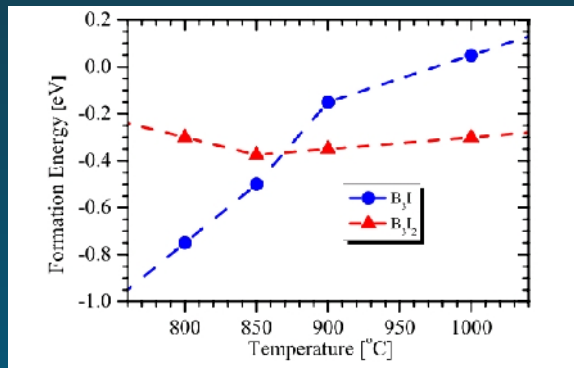


Fig. 8. Simulation results for Spike and Flash Anneal

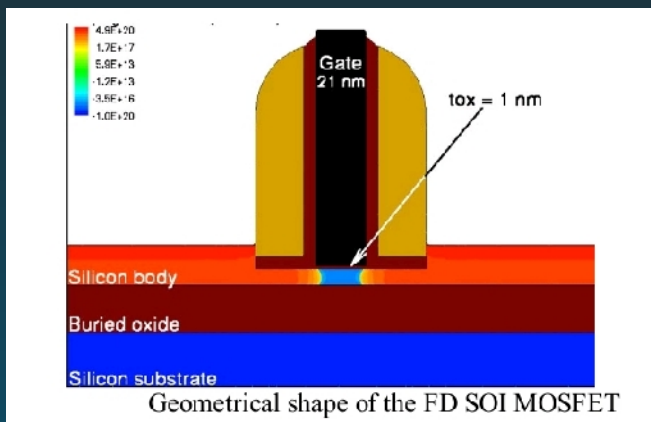
J. Schermer et al., ESSDERC 2007 (PULLNANO results)

Boron diffusion modeling & Device simulation

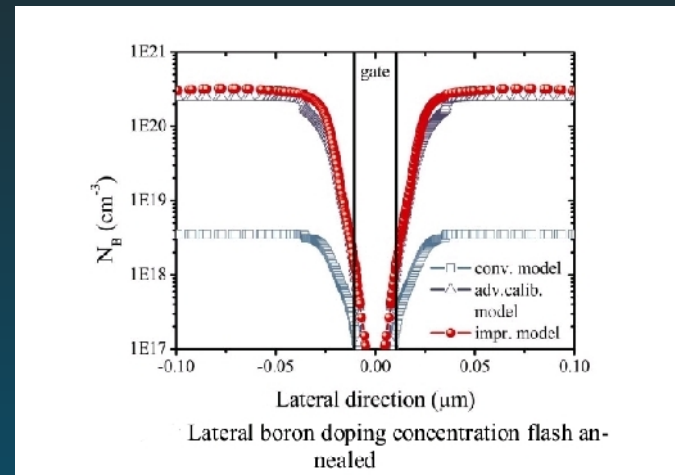
Process Models for Advanced Annealing Schemes and their Use in Device Simulation

P. Pichler^{1,2,*}, A. Martinez-Limia¹, C. Kampen¹, A. Burenkov¹, J. Schermer¹, S. Paul³, W. Lerch³,
J. Gelpy⁴, S. McCoy⁴, H. Kheyrandish⁵, A. Pakfar⁶, C. Tavernier⁶, D. Bolze⁷

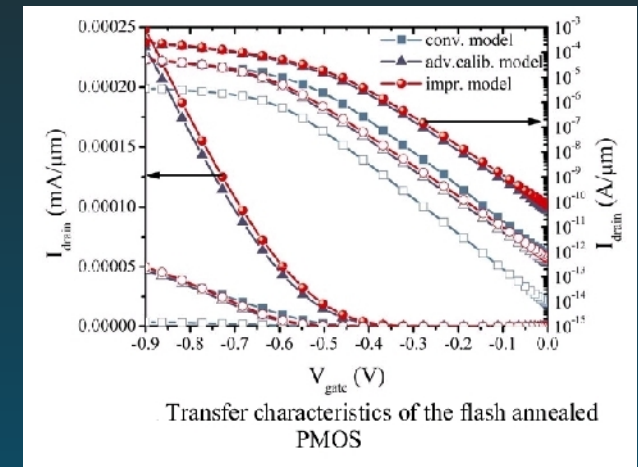
¹Fraunhofer-Institute of Integrated Systems and Device Technology (IISB),
Schottkystrasse 10, 91058 Erlangen, Germany



FD nanometric SOI device



Impact of the diffusion modeling on the boron profile

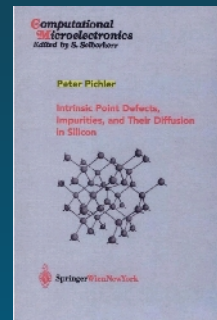


Large impact on the PMOS electrical characteristic predicted

P. Pichler et al., International Workshop on junction Technology (2008), ATOMICS & PULLNANO Results

Conclusion

- Large progress have been done in junction processing modeling in the framework of several european projects (Rapid, Frenotech, Pullnano, Atomics) with the collaboration of Synopsys (Zurich)
- Some of the models presented (simplified form) in Sentaurus Process or script transfered to semiconductor compagnies
- But still a lot of work:
 - Influence of stress effects
 - New Material (SiGe S/D, Ge.....)
 - Advanced annealing scheme (laser annealing, solid phase epitaxy)
- More information :



Part V (prospective)

Atomistic TCAD : towards some computer experiment ?

Complexity & Limits of a full experimental optimisation (1) ?

- Complex integration in nanodevices

APPLIED PHYSICS LETTERS 90, 241912 (2007)

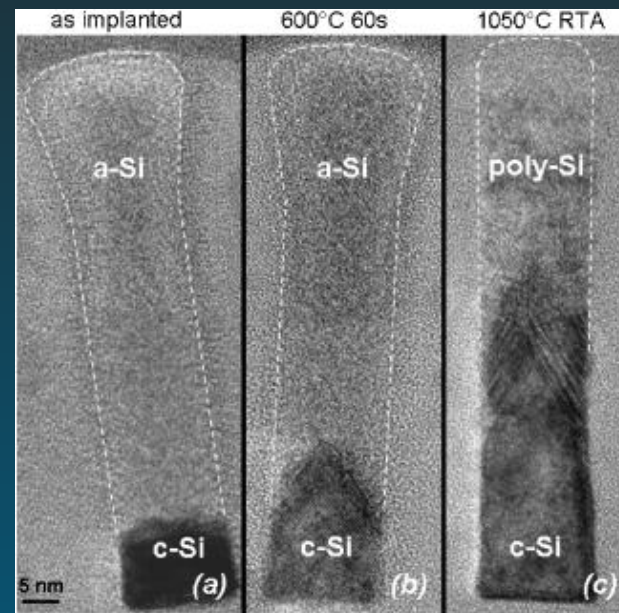
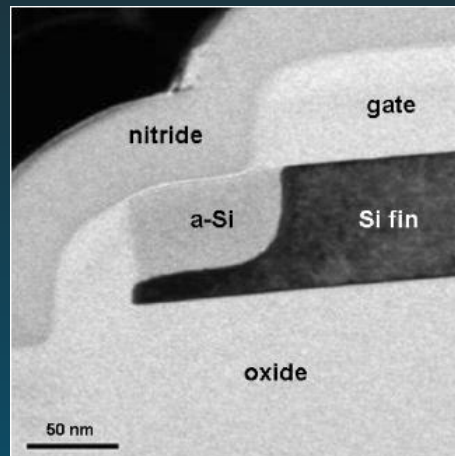
Solid phase epitaxy versus random nucleation and growth in sub-20 nm wide fin field-effect transistors

R. Duřty,^{a)} M. J. H. Van Dal, and B. J. Pawlak
NXP Semiconductors, Kapeldreef 75, 3001 Leuven, Belgium

M. Kaiser and R. G. R. Weemaes
Philips Research Laboratories Eindhoven, High Tech Campus 11, 5656 AE Eindhoven, The Netherlands

B. Degroote, E. Kunnen, and E. Altamirano
IMEC, Kapeldreef 75, 3001 Leuven, Belgium

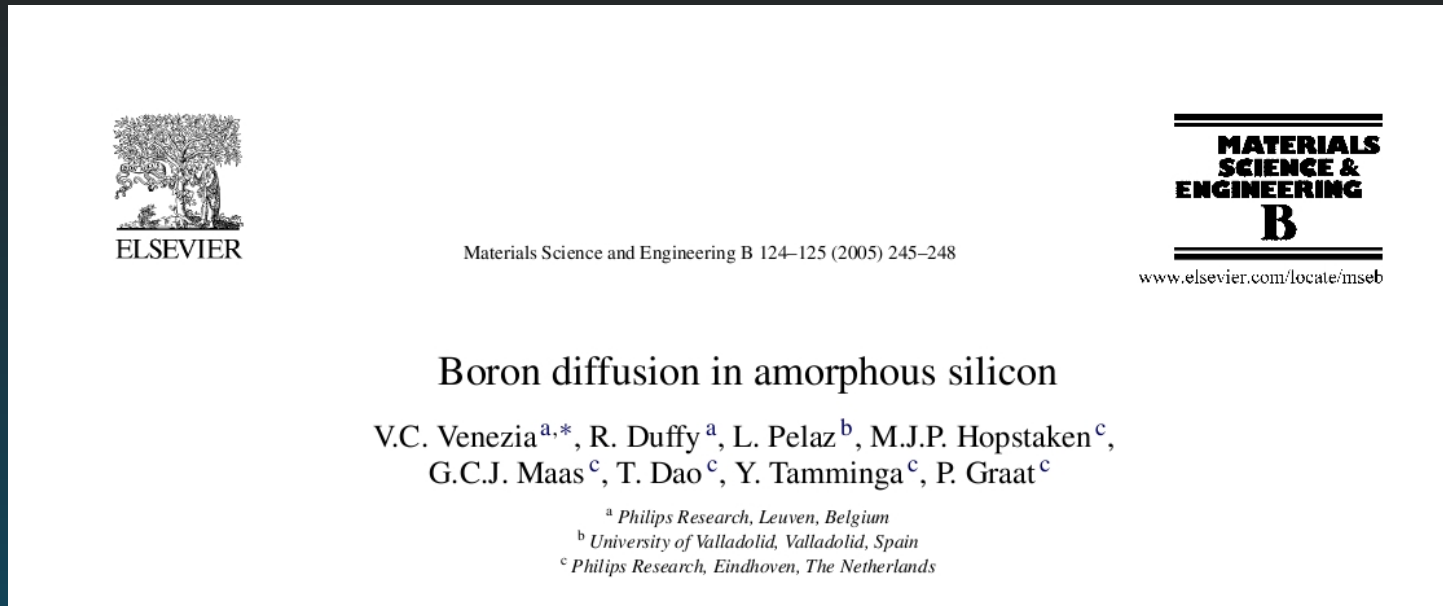
(Received 26 March 2007; accepted 22 May 2007; published online 13 June 2007)



(PULLNANO results)

Complexity & Limits of a full experimental optimisation (2) ?

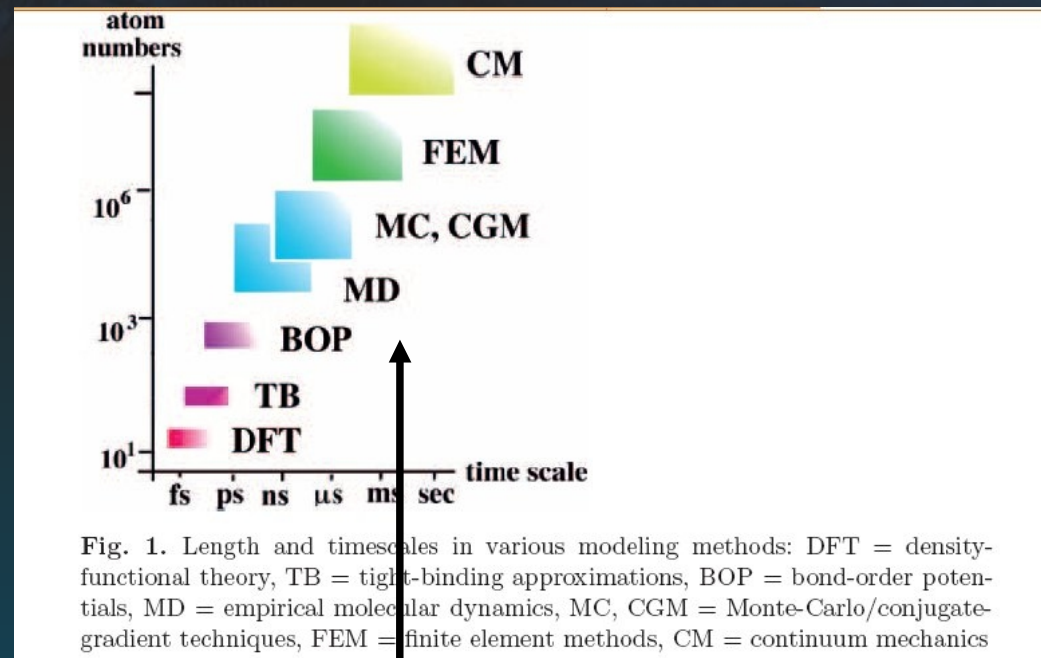
How to characterised diffusion mechanism during a solid phase epitaxy when Time/Temperature window available reduced by recrystallisation ?



→ A solution proposed by Venezia et al.: Diffusion in completely amorphised silicon layer (but the influence of recrystallisation is not taken into account)

→ Computer experiment (Atomistic TCAD) needed but it will not replace standard TCAD !

Which method for computer experiment ?



[Scheerschmidt07] http://www.mpi-halle.de/mpi/publi/pdf/6735_06.pdf

Development of atomistic approach based on molecular dynamics (MD)

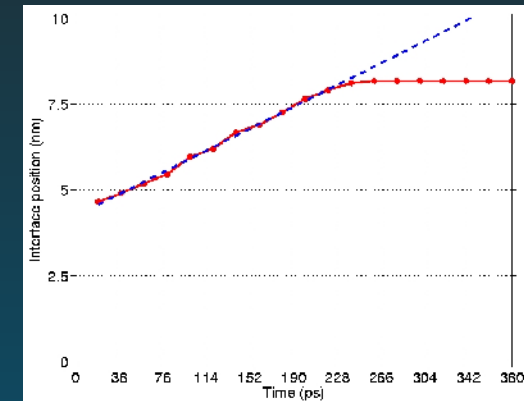
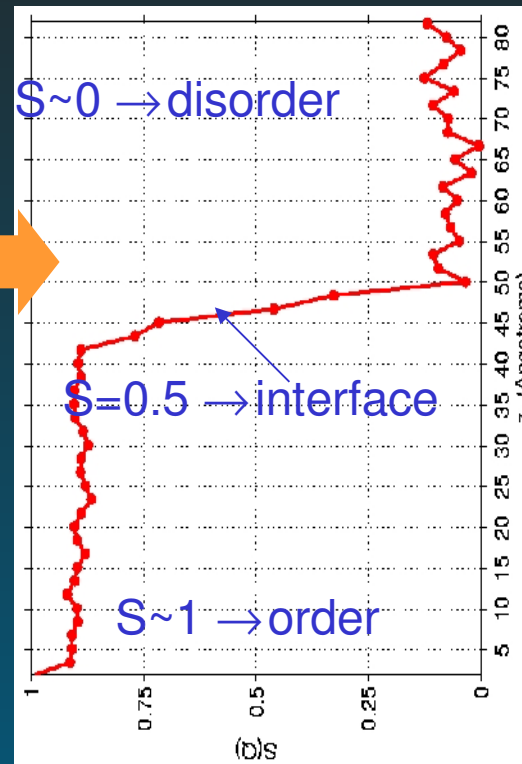
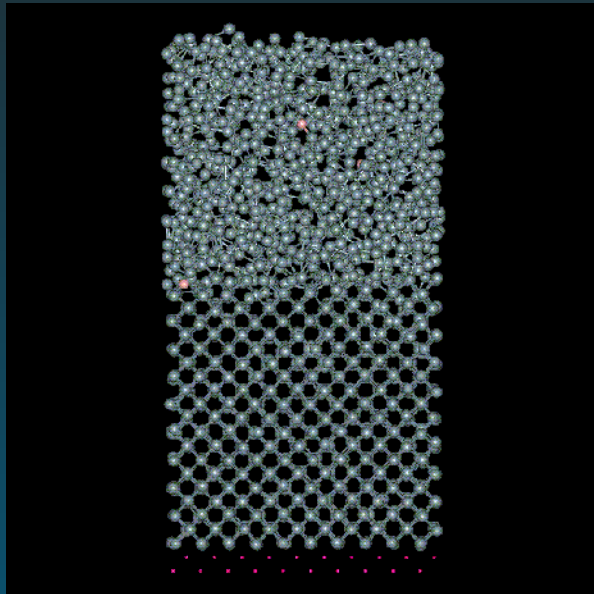
Molecular Dynamics of LPE, SPE regrowth

Simulation of the annealing and exploitation

Example of annealing, Stillinger-Weber, 1200 K

Extraction interface
from 1D structure factor

Procedure repeated to extract
the recrystallization velocity

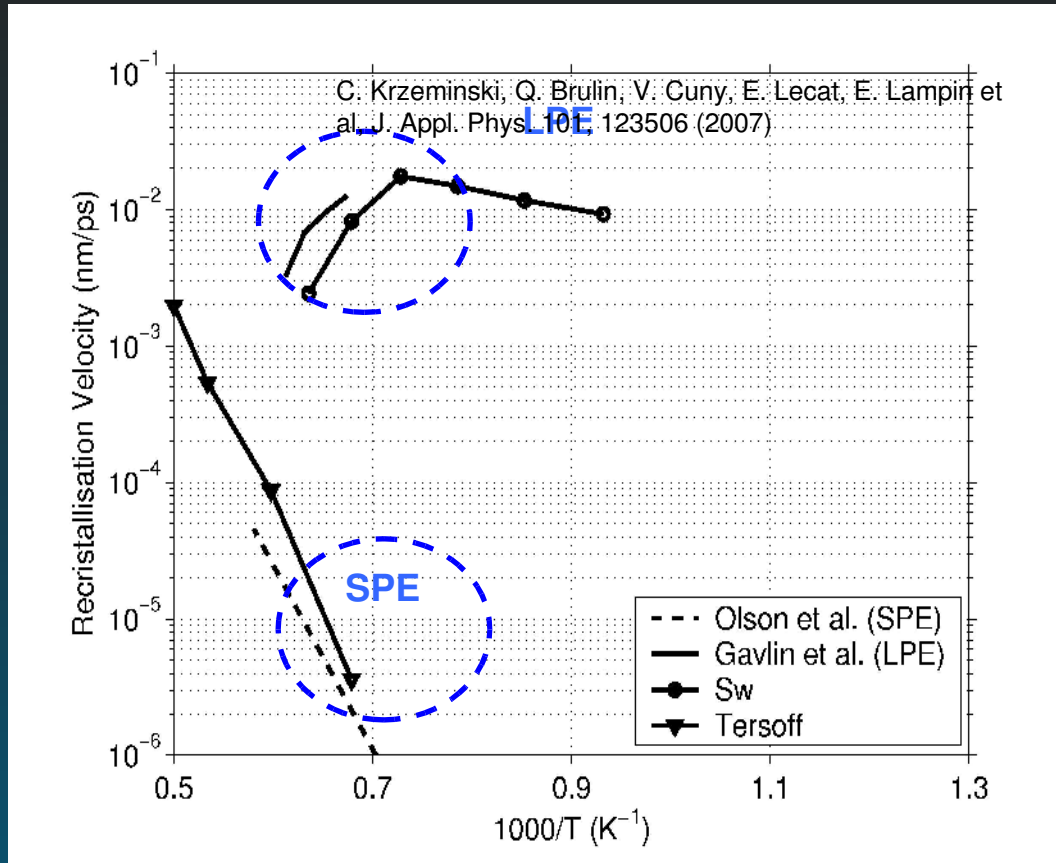


Extraction of the position of
the interface vs time

Molecular dynamics of SPE, LPE regrowth (2)

Conclusion :

Analysis of the velocities of recrystallization and of the structure of disordered part :



Potentiality to simulate both SPE and LPE

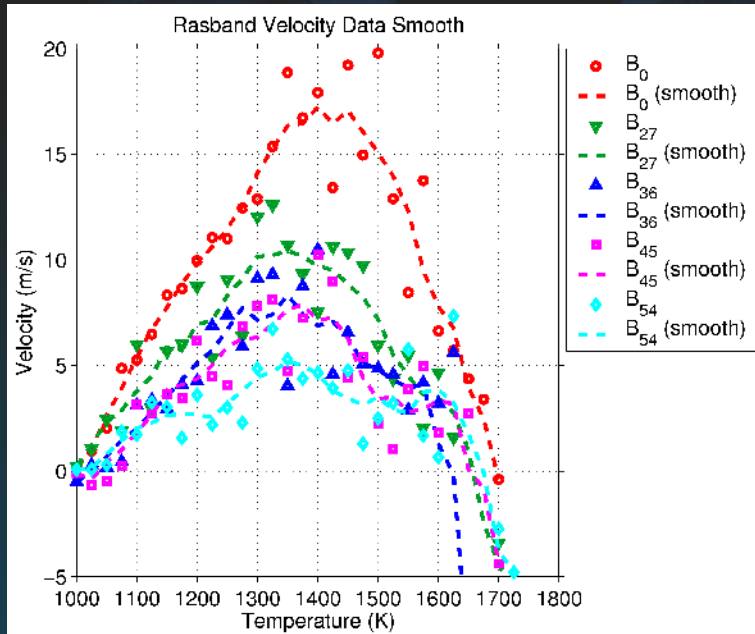
SPER or flash annealing

Laser annealing

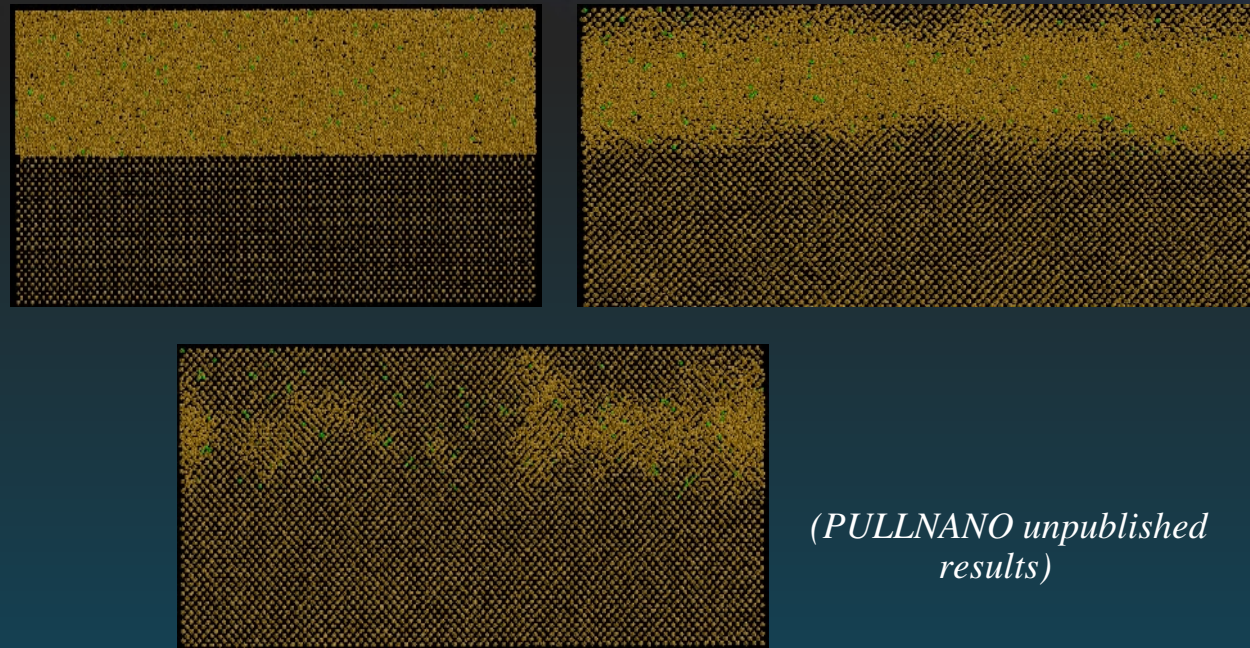
(PULLNANO results)

Boron doped LPE regrowth

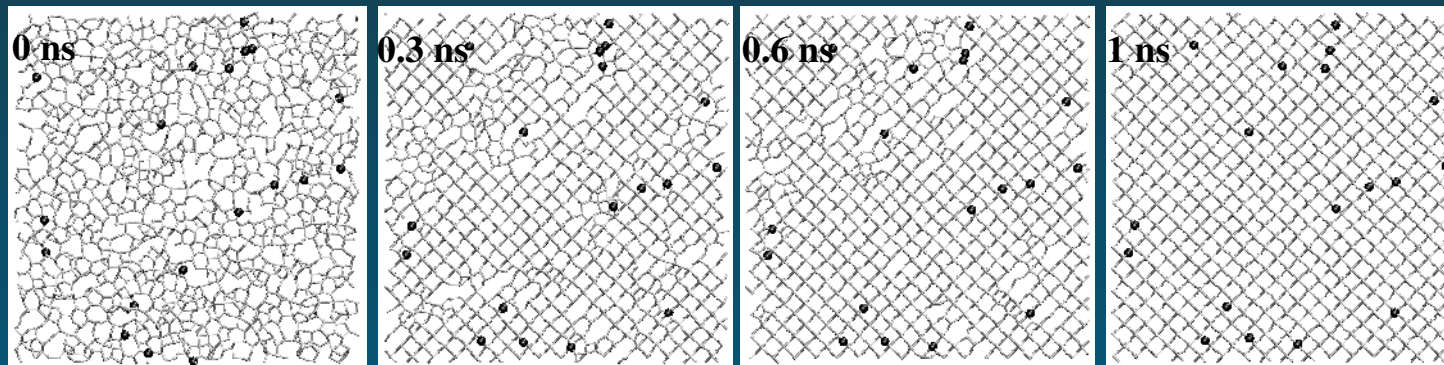
Reduction of the velocity for large B concentration



Interface roughening & amorphous pockets



Incorporation of boron atoms in c-Si

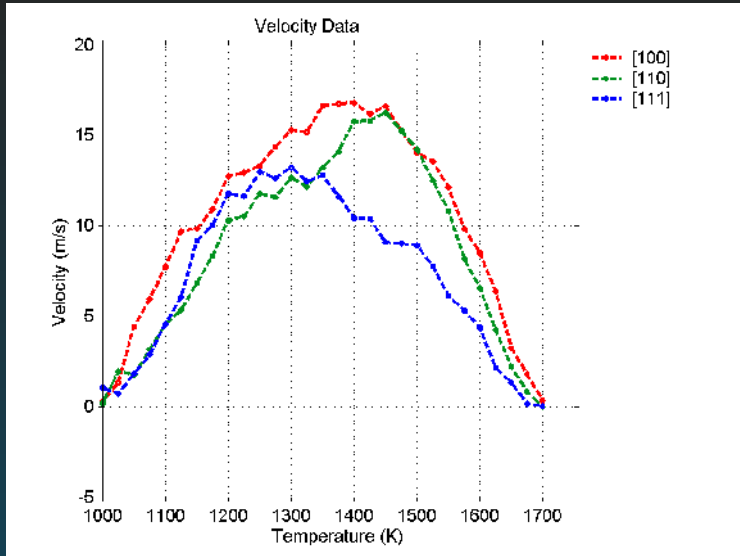


A. Mattoni and L. Colombo,
Phys. Rev. B 69 (2004) 045204

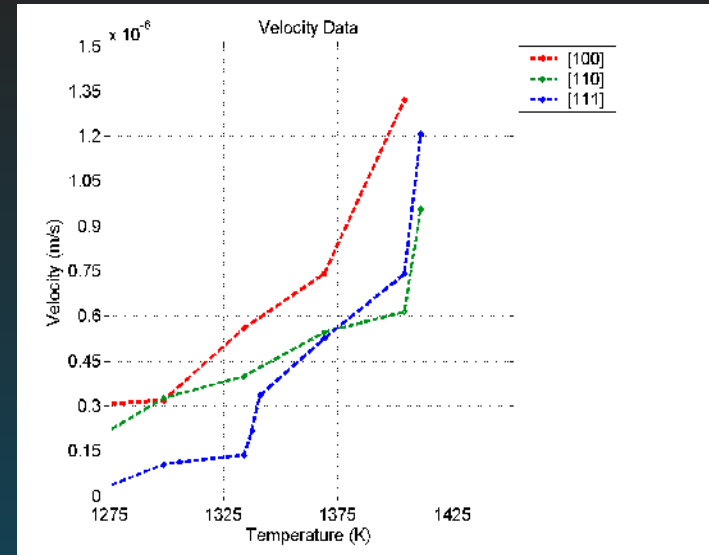
PULLNANO



LPE or SPE: influence orientation effects



Orientation influence for LPE $[100] > [110] > [111]$



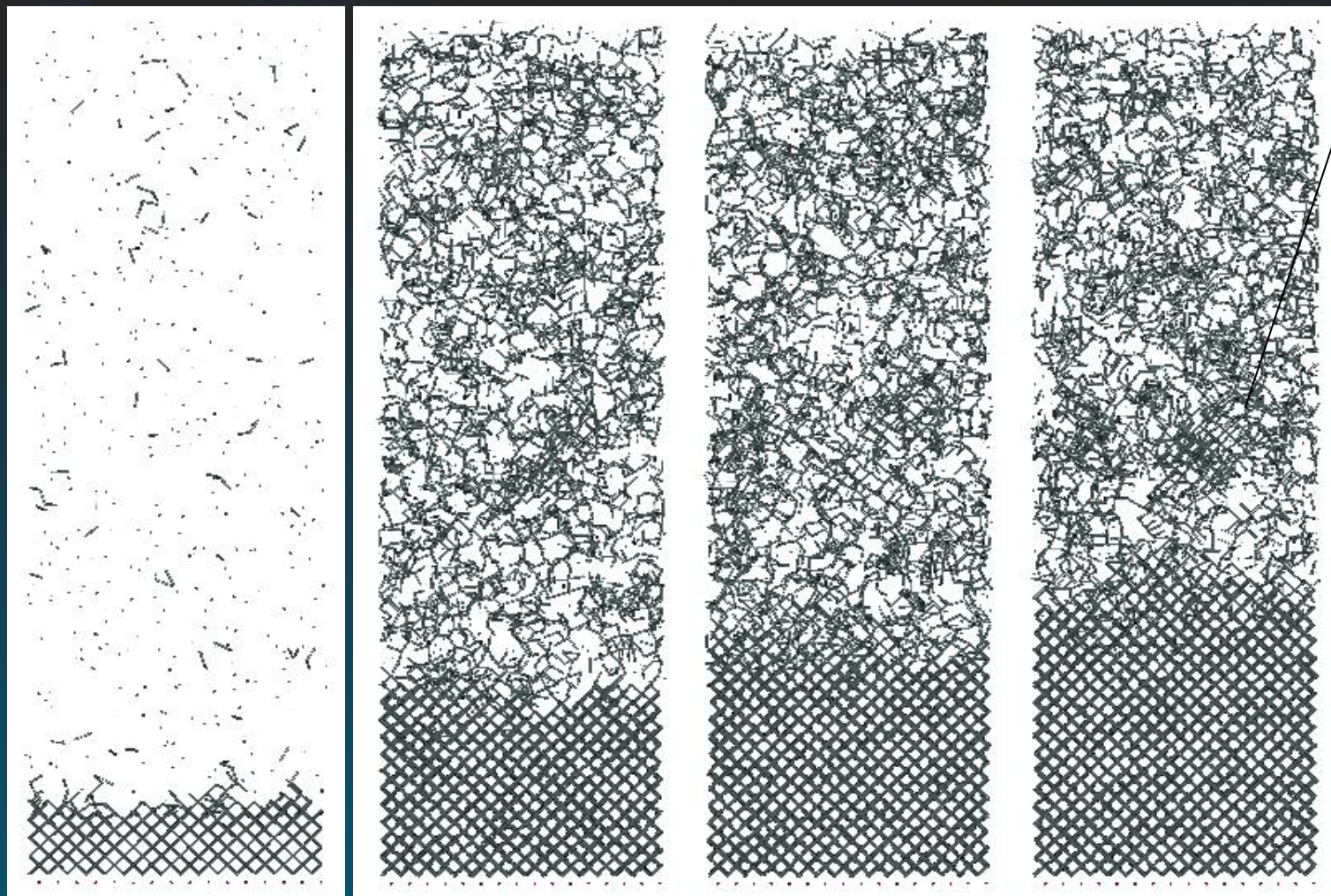
Orientation influence for SPE $[100] > [110] > [111]$

(PULLNANO unpublished results)

Competition SPE/RNG

Thick amorphous layer

Some grains begin to form by RNG



Thin crystalline germ

Crystallization has progressed by SPE

30 ns

60 ns

80 ns

(PULLNANO unpublished results)

